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# 1. Introduction

The LA-MachXO automotive device family is optimized to meet the requirements of applications traditionally addressed by CPLDs and low capacity FPGAs: glue logic, bus bridging, bus interfacing, power-up control, and control logic. These devices bring together the best features of CPLD and FPGA devices on a single chip in AEC-Q100 tested and qualified versions.

The devices use look-up tables (LUTs) and embedded block memories traditionally associated with FPGAs for flexible and efficient logic implementation. Through nonvolatile technology, the devices provide the single-chip, high-security, instant-on capabilities traditionally associated with CPLDs. Finally, advanced process technology and careful design will provide the high pin-to-pin performance also associated with CPLDs.

The ispLEVER<sup>®</sup> design tools from Lattice allow complex designs to be efficiently implemented using the LAMachXO automotive family of devices. Popular logic synthesis tools provide synthesis library support for LAMachXO. The ispLEVER tools use the synthesis tool output along with the constraints from its floor planning tools to place and route the design in the LA-MachXO device. The ispLEVER tool extracts the timing from the routing and back-annotates it into the design for timing verification.

# 2. Features

- Non-volatile, Infinitely Reconfigurable
  - Instant-on powers up in microseconds
  - Single chip, no external configuration memory required
  - Excellent design security, no bit stream to intercept
  - Reconfigure SRAM based logic in milliseconds
  - SRAM and non-volatile memory programmable through JTAG port
  - Supports background programming of non-volatile memory
  - AEC-Q100 Tested and Qualified
- Sleep Mode
  - Allows up to 100x static current reduction
- TransFR<sup>™</sup> Reconfiguration (TFR)
  - In-field logic update while system operates
- High I/O to Logic Density
  - 256 to 2280 LUT4s
  - 73 to 271 I/Os with extensive package options
  - Density migration supported
  - Lead free/RoHS compliant packaging
- Embedded and Distributed Memory
  - Up to 27.6 Kbits sysMEM<sup>™</sup> Embedded Block RAM
  - Up to 7.5 Kbits distributed RAM
  - Dedicated FIFO control logic
- Flexible I/O Buffer
- Programmable sysIO<sup>™</sup> buffer supports wide range of interfaces:
  - LVCMOS 3.3/2.5/1.8/1.5/1.2
  - LVTTL
  - PCI
  - LVDS, Bus-LVDS, LVPECL, RSDS



- sysCLOCK<sup>™</sup> PLLs
  - Up to two analog PLLs per device
  - Clock multiply, divide, and phase shifting
- System Level Support
  - IEEE Standard 1149.1 Boundary Scan
  - Onboard oscillator
  - Devices operate with 3.3 V, 2.5 V, 1.8V or 1.2 V power supply
  - IEEE 1532 compliant in-system programming

#### Table 2.1. LA-MachXO Automotive Family Selection Guide

Device	LAMXO256E/C	LAMXO640E/C	LAMXO1200E	LAMXO2280E
LUTs	256	640	1200	2280
Dist. RAM (Kbits)	2.0	6.0	6.25	7.5
EBR SRAM (Kbits)	0	0	9.2	27.6
Number of EBR SRAM Blocks (9 Kbits)	0	0	1	3
V <sub>CC</sub> Voltage	1.2/1.8/2.5/3.3V	1.2/1.8/2.5/3.3V	1.2	1.2
Number of PLLs	0	0	1	2
Max. I/O	78	159	211	271
Packages				
100-pin Lead-Free TQFP (14x14 mm)	78	74	73	73
144-pin Lead-Free TQFP (20x20 mm)		113	113	113
256-ball Lead-Free ftBGA (17x17 mm)		159	211	211
324-ball Lead-Free ftBGA (19x19 mm)				271

# 3. Architecture

## **3.1.** Architecture Overview

The LA-MachXO family architecture contains an array of logic blocks surrounded by Programmable I/O (PIO). Some devices in this family have sysCLOCK PLLs and blocks of sysMEM<sup>™</sup> Embedded Block RAM (EBRs). Figure 3.1., Figure 3.2., and Figure 3.3. show the block diagrams of the various family members.

The logic blocks are arranged in a two-dimensional grid with rows and columns. The EBR blocks are arranged in a column to the left of the logic array. The PIO cells are located at the periphery of the device, arranged into Banks. The PIOs utilize a flexible I/O buffer referred to as a sysIO interface that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

There are two kinds of logic blocks, the Programmable Functional Unit (PFU) and the Programmable Functional unit without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM, ROM, and register functions. The PFF block contains building blocks for logic, arithmetic, ROM, and register functions. Both the PFU and PFF blocks are optimized for flexibility, allowing complex designs to be implemented quickly and effectively. Logic blocks are arranged in a two-dimensional array. Only one type of block is used per row.

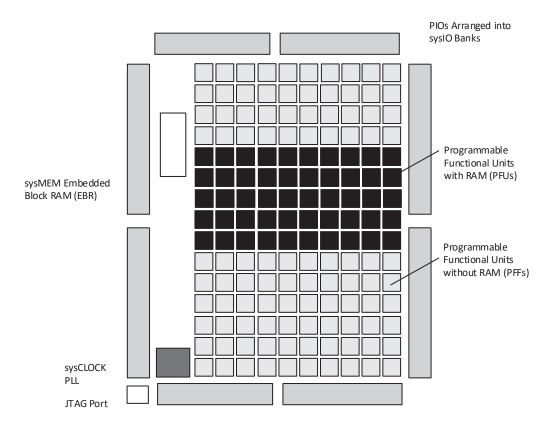
In the LA-MachXO family, the number of sysIO Banks varies by device. There are different types of I/O Buffers on different Banks. See the details in later sections of this document. The sysMEM EBRs are large, dedicated fast memory blocks; these blocks are found only in the larger devices. These blocks can be configured as RAM, ROM or FIFO. FIFO support includes dedicated FIFO pointer and flag "hard" control logic to minimize LUT use.

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The LA-MachXO architecture provides up to two sysCLOCK<sup>™</sup> Phase Locked Loop (PLL) blocks on larger devices. These blocks are located at either end of the memory blocks. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

Every device in the family has a JTAG Port that supports programming and configuration of the device as well as access to the user logic. The LA-MachXO devices are available for operation from 3.3 V, 2.5 V, 1.8 V, and 1.2 V power supplies, providing easy integration into the overall system.



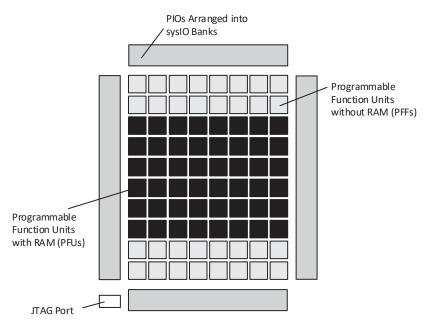
1. Top view of the LA-MachXO2280 device is similar but with higher LUT count, two PLLs, and three EBR blocks.

Figure 3.1. Top View of the LA-MachXO1200 Device<sup>1</sup>

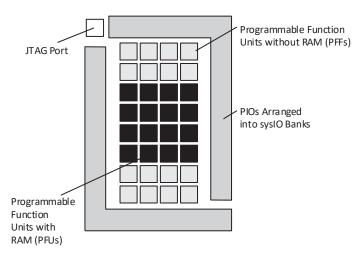
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### 3.1.1. PFU Blocks

The core of the LA-MachXO devices consists of PFU and PFF blocks. The PFUs can be programmed to perform Logic, Arithmetic, Distributed RAM, and Distributed ROM functions. PFF blocks can be programmed to perform Logic, Arithmetic, and Distributed ROM functions. Except where necessary, the remainder of this data sheet will use the term PFU to refer to both PFU and PFF blocks.

Each PFU block consists of four interconnected Slices, numbered 0-3 as shown in Figure 3.4. There are 53 inputs and 25 outputs associated with each PFU block.

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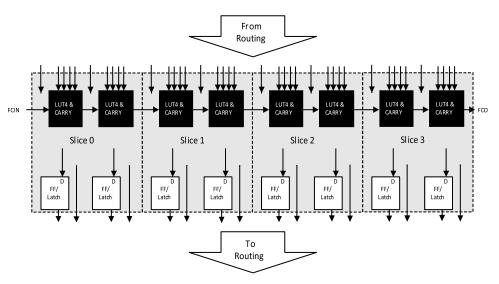


Figure 3.4. PFU Diagram

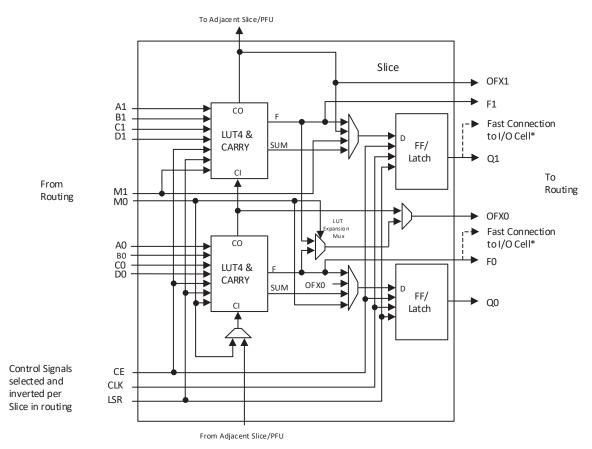
## 3.1.2. Slice

Each Slice contains two LUT4 lookup tables feeding two registers (programmed to be in FF or Latch mode), and some associated logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7, and LUT8. There is control logic to perform set/reset functions (programmable as synchronous/asynchronous), clock select, chip-select, and wider RAM/ROM functions. Figure 3.5. shows an overview of the internal logic of the Slice. The registers in the Slice can be configured for positive/negative and edge/level clocks.

There are 14 input signals: 13 signals from routing and one from the carry-chain (from the adjacent Slice/PFU). There are 7 outputs: 6 to the routing and one to the carry-chain (to the adjacent Slice/PFU). Table 3.1. lists the signals associated with each Slice.

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Notes:

Some inter-Slice signals are not shown. \* Only PFUs at the edges have fast connections to the I/O cell.

U				
	Function	Туре	Signal Names	Descripti
	Input	Data signal	A0, B0, C0, D0	Inputs to
	Input	Data signal	A1, B1, C1, D1	Inputs to
	Input	Multi-purpose	M0/M1	Multipur

Table 3.1. Slice Signal Descri	ptions
--------------------------------	--------

Function	Туре	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0/M1	Multipurpose Input
Input	Control signal	CE	Clock Enable
Input	Control signal	LSR	Local Set/Reset
Input	Control signal	CLK	System Clock
Input	Inter-PFU signal	FCIN	Fast Carry In <sup>1</sup>
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register Outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8 <sup>2</sup> MUX depending on the Slice
Output	Inter-PFU signal	FCO	Fast Carry Out <sup>1</sup>

#### Notes:

See Figure 3.4. for connection details. 1.

2. Requires two PFUs.

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#### **Modes of Operation**

Each Slice is capable of four modes of operation: Logic, Ripple, RAM, and ROM. The Slice in the PFF is capable of all modes except RAM. Table 3.2. lists the modes and the capability of the Slice blocks.

#### Table 3.2. Slice Modes

	Logic	Ripple	RAM	ROM
PFU Slice	LUT 4x2 or LUT 5x1	2-bit Arithmetic Unit	SP 16x2	ROM 16x1 x 2
PFF Slice	LUT 4x2 or LUT 5x1	2-bit Arithmetic Unit	N/A	ROM 16x1 x 2

#### Logic Mode:

In this mode, the LUTs in each Slice are configured as 4-input combinatorial lookup tables (LUT4). A LUT4 can have 16 possible input combinations. Any logic function with four inputs can be generated by programming this lookup table. Since there are two LUT4s per Slice, a LUT5 can be constructed within one Slice. Larger lookup tables such as LUT6, LUT7, and LUT8 can be constructed by concatenating other Slices.

**Ripple Mode:** Ripple mode allows the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each Slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Ripple mode multiplier building block
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Two additional signals, Carry Generate and Carry Propagate, are generated per Slice in this mode, allowing fast arithmetic functions to be constructed by concatenating Slices.

**RAM Mode:** In this mode, distributed RAM can be constructed using each LUT block as a 16x2-bit memory. Through the combination of LUTs and Slices, a variety of different memories can be constructed.

The ispLEVER design tool supports the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 3.3. shows the number of Slices required to implement different distributed RAM primitives. Figure 3.6. shows the distributed memory primitive block diagrams. Dual port memories involve the pairing of two Slices. One Slice functions as the read-write port, while the other companion Slice supports the read-only port. For more information on RAM mode in LA-MachXO devices, please see details of additional technical documentation at the end of this data sheet.

#### Table 3.3. Number of Slices Required For Implementing Distributed RAM

	SPR16x2	DPR16x2
Number of Slices	1	2

**Note:** SPR = Single Port RAM, DPR = Dual Port RAM

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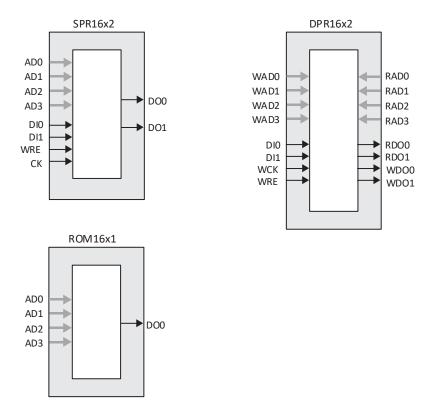


Figure 3.6. Distributed Memory Primitives

#### **ROM Mode:**

The ROM mode uses the same principal as the RAM modes, but without the Write port. Pre-loading is accomplished through the programming interface during configuration.

#### **PFU Modes of Operation**

Slices can be combined within a PFU to form larger functions. Table 3.7. tabulates these modes and documents the functionality possible at the PFU level.

Logic	Ripple	RAM	ROM
LUT 4x8 or MUX 2x1 x 8	2-bit Add x 4	SPR16x2 x 4	ROM16x1 x 8
		DPR16x2 x 2	
LUT 5x4 or MUX 4x1 x 4	2-bit Sub x 4	SPR16x4 x 2	ROM16x2 x 4
		DPR16x4 x 1	
LUT 6x 2 or MUX 8x1 x 2	2-bit Counter x 4	SPR16x8 x 1	ROM16x4 x 2
LUT 7x1 or MUX 16x1 x 1	2-bit Comp x 4		ROM16x8 x 1

#### Table 3.4. PFU Modes of Operation

### 3.1.3. Routing

There are many resources provided in the LA-MachXO devices to route signals individually or as buses with related control signals. The routing resources consist of switching circuitry, buffers and metal interconnect (routing) segments.

The inter-PFU connections are made with three different types of routing resources: x1 (spans two PFUs), x2 (spans three PFUs) and x6 (spans seven PFUs). The x1, x2, and x6 connections provide fast and efficient connections in the horizontal and vertical directions.

The ispLEVER design tool takes the output of the synthesis tool and places and routes the design. Generally, the place and route tool is completely automatic, although an interactive routing editor is available to optimize the design.

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## 3.2. Clock/Control Distribution Network

The LA-MachXO automotive family of devices provides global signals that are available to all PFUs. These signals consist of four primary clocks and four secondary clocks. Primary clock signals are generated from four 16:1 muxes as shown in Figure 3.7. and Figure 3.8. The available clock sources for the LA-MachXO256 and LA-MachXO640 devices are four dual function clock pins and 12 internal routing signals. The available clock sources for the LAMachXO1200 and LA-MachXO2280 devices are four dual function clock pins, up to nine internal routing signals and up to six PLL outputs.

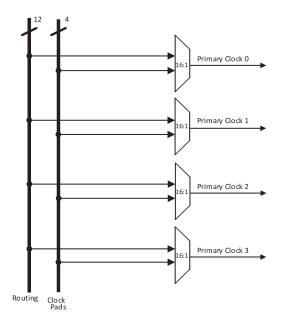


Figure 3.7. Primary Clocks for LA-MachXO256 and LA-MachXO640 Devices

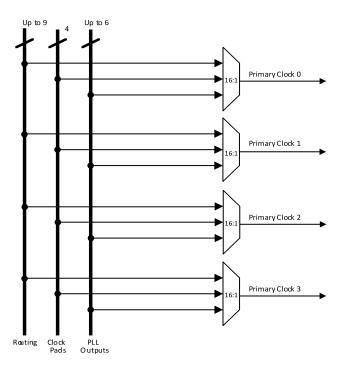


Figure 3.8. Primary Clocks for LA-MachXO1200 and LA-MachXO2280 Devices

Four secondary clocks are generated from four 16:1 muxes as shown in Figure 3.9. Four of the secondary clock sources come from dual function clock pins and 12 come from internal routing.

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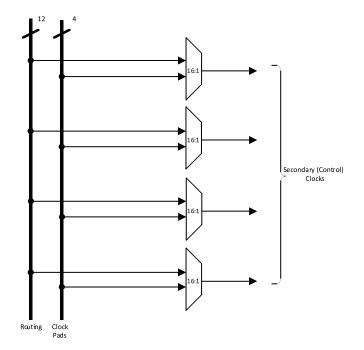


Figure 3.9. Secondary Clocks for LA-MachXO Devices

## 3.2.1. sysCLOCK Phase Locked Loops (PLLs)

The LA-MachXO1200 and LA-MachXO2280 provide PLL support. The source of the PLL input divider can come from an external pin or from internal routing. There are four sources of feedback signals to the feedback divider: from CLKINTFB (internal feedback port), from the global clock nets, from the output of the post scalar divider, and from the routing (or from an external pin). There is a PLL\_LOCK signal to indicate that the PLL has locked on to the input clock signal. Figure Figure 3.10. shows the sysCLOCK PLL diagram.

The setup and hold times of the device can be improved by programming a delay in the feedback or input path of the PLL which will advance or delay the output clock with reference to the input clock. This delay can be either programmed during configuration or can be adjusted dynamically. In dynamic mode, the PLL may lose lock after

adjustment and not relock until the  $t_{LOCK}$  parameter has been satisfied. Additionally, the phase and duty cycle block allows the user to adjust the phase and duty cycle of the CLKOS output.

The sysCLOCK PLLs provide the ability to synthesize clock frequencies. Each PLL has four dividers associated with it: input clock divider, feedback divider, post scalar divider, and secondary clock divider. The input clock divider is used to divide the input clock signal, while the feedback divider is used to multiply the input clock signal. The post scalar divider allows the VCO to operate at higher frequencies than the clock output, thereby increasing the frequency range. The secondary divider is used to derive lower frequency outputs.

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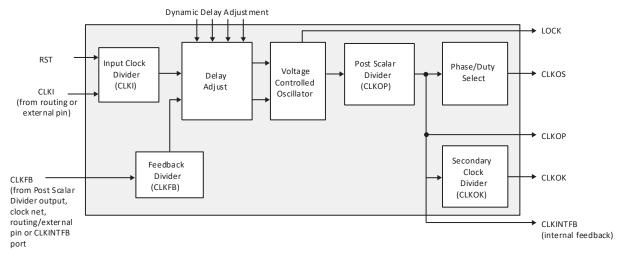
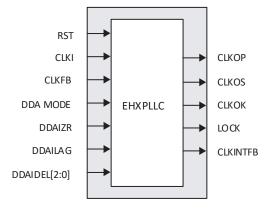


Figure 3.10. PLL Diagram

Figure 3.11. shows the available macros for the PLL. Table 3.5. provides signal description of the PLL Block.





#### **Table 3.5. PLL Signal Descriptions**

Signal	I/O	Description
CLKI	I	Clock input from external pin or routing
CLKFB	I	PLL feedback input from PLL output, clock net, routing/external pin or internal feedback from CLKINTFB port
RST	I	"1" to reset the input clock divider
CLKOS	0	PLL output clock to clock tree (phase shifted/duty cycle changed)
CLKOP	0	PLL output clock to clock tree (No phase shift)
CLKOK	0	PLL output to clock tree through secondary clock divider
LOCK	0	"1" indicates PLL LOCK to CLKI
CLKINTFB	0	Internal feedback source, CLKOP divider output before CLOCKTREE
DDAMODE	I	Dynamic Delay Enable. "1": Pin control (dynamic), "0": Fuse Control (static)
DDAIZR	I	Dynamic Delay Zero. "1": delay = 0, "0": delay = on
DDAILAG	I	Dynamic Delay Lag/Lead. "1": Lag, "0": Lead
DDAIDEL[2:0]	I	Dynamic Delay Input

For more information on the PLL, please see details of additional technical documentation at the end of this data sheet.

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## 3.3. sysMEM Memory

The LA-MachXO1200 and LA-MachXO2280 devices contain sysMEM Embedded Block RAMs (EBRs). The EBR consists of a 9-Kbit RAM, with dedicated input and output registers.

### sysMEM Memory Block

The sysMEM block can implement single port, dual port, pseudo dual port, or FIFO memories. Each block can be used in a variety of depths and widths as shown in Table 3.6.

Table 3.6. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	8,192 x 1
	4,096 x 2
	2,048 x 4
	1,024 x 9
	512 x 18
	256 x 36
True Dual Port	8,192 x 1
	4,096 x 2
	2,048 x 4
	1,024 x 9
	512 x 18
Pseudo Dual Port	8,192 x 1
	4,096 x 2
	2,048 x 4
	1,024 x 9
	512 x 18
	256 x 36
FIFO	8,192 x 1
	4,096 x 2
	2,048 x 4
	1,024 x 9
	512 x 18
	256 x 36

#### **Bus Size Matching**

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1 and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

### **RAM Initialization and ROM Operation**

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

#### **Memory Cascading**

Larger and deeper blocks of RAMs can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

#### Single, Dual, Pseudo-Dual Port and FIFO Modes

Figure 3.12. shows the five basic memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and address for the ports are registered at the input of the memory array. The output data of the memory is optionally registered at the memory array output.



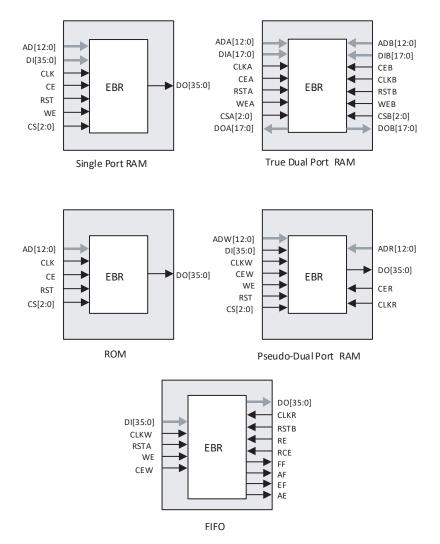


Figure 3.12. sysMEM Memory Primitives

The EBR memory supports three forms of write behavior for single or dual port operation:

- 1. **Normal** data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
- 2. Write Through a copy of the input data appears at the output of the same port. This mode is supported for all data widths.
- 3. **Read-Before-Write** when new data is being written, the old contents of the address appears at the output. This mode is supported for x9, x18 and x36 data widths.

#### **FIFO Configuration**

The FIFO has a write port with Data-in, CEW, WE and CLKW signals. There is a separate read port with Data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. The range of programming values for these flags are in Table 3.7.



#### Table 3.7. sysMEM Block Configurations

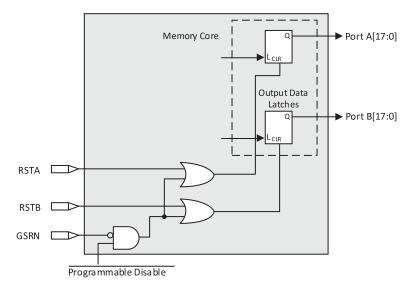
Flag Name	Programming Range
Full (FF)	1 to (up to 2 <sup>N</sup> -1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

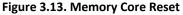
Note: N = Address bit width

The FIFO state machine supports two types of reset signals: RSTA and RSTB. The RSTA signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset state. The RSTB signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

#### **Memory Core Reset**

The memory array in the EBR utilizes latches at the A and B output ports. These latches can be reset asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with Port A and Port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 3.13.





For further information on the sysMEM EBR block, see the details of additional technical documentation at the end of this data sheet.

#### **EBR Asynchronous Reset**

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 3.14. The GSR input to the EBR is always asynchronous.



Reset	
Clock	
Clock Enable	

Figure 3.14. EBR Asynchronous Reset (Including GSR) Timing Diagram

If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of  $1/f_{MAX}$  (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

If an EBR is pre-loaded during configuration, the GSR input must be disabled or the release of the GSR during device Wake Up must occur before the release of the device I/Os becoming active.

These instructions apply to all EBR RAM, ROM and FIFO implementations. For the EBR FIFO mode, the GSR signal is always enabled and the WE and RE signals act like the clock enable signals in Figure 3.14. The reset timing rules apply to the RPReset input vs the RE input and the RST input vs. the WE and RE inputs. Both RST and RPReset are always asynchronous EBR inputs.

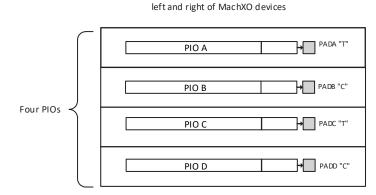
Note that there are no reset restrictions if the EBR synchronous reset is used and the EBR GSR input is disabled.

## 3.4. PIO Groups

On the LA-MachXO devices, PIO cells are assembled into two different types of PIO groups, those with four PIO cells and those with six PIO cells. PIO groups with four IOs are placed on the left and right sides of the device while PIO groups with six IOs are placed on the top and bottom. The individual PIO cells are connected to their respective sysIO buffers and PADs.

On all LA-MachXO devices, two adjacent PIOs can be joined to provide a complementary Output driver pair. The I/ O pin pairs are labeled as "T" and "C" to distinguish between the true and complement pins.

The LA-MachXO1200 and LA-MachXO2280 devices contain enhanced I/O capability. All PIO pairs on these larger devices can implement differential receivers. In addition, half of the PIO pairs on the left and right sides of these devices can be configured as LVDS transmit/receive pairs. PIOs on the top of these larger devices also provide PCI support.



This structure is used on the

Figure 3.15. Group of Four Programmable I/O Cells

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This structure is used on the top and bottom of MachXO devices

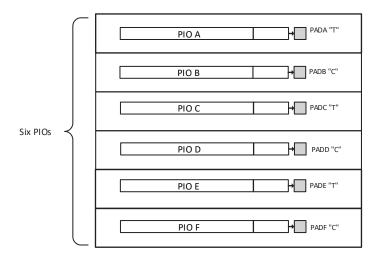


Figure 3.16. Group of Six Programmable I/O Cells

### 3.4.1. PIO

The PIO blocks provide the interface between the sysIO buffers and the internal PFU array blocks. These blocks receive output data from the PFU array and a fast output data signal from adjacent PFUs. The output data and fast output data signals are multiplexed and provide a single signal to the I/O pin via the sysIO buffer. Figure 3.17. shows the LA-MachXO PIO logic.

The tristate control signal is multiplexed from the output data signals and their complements. In addition a global signal (TSALL) from a dedicated pad can be used to tristate the sysIO buffer.

The PIO receives an input signal from the pin via the sysIO buffer and provides this signal to the core of the device. In addition there are programmable elements that can be utilized by the design tools to avoid positive hold times.

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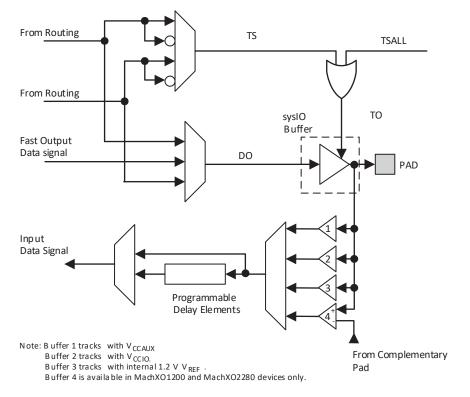


Figure 3.17. LA-MachXO PIO Block Diagram

## 3.5. sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as Banks. The sysIO buffers allow users to implement the wide variety of standards that are found in today's systems including LVCMOS, TTL, BLVDS, LVDS and LVPECL.

In the LA-MachXO devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using  $V_{CCIO}$ . In addition to the Bank  $V_{CCIO}$  supplies, the LA-MachXO devices have a  $V_{CC}$  core logic power supply, and a  $V_{CCAUX}$  supply that powers up a variety of internal circuits including all the differential and referenced input buffers.

LA-MachXO256 and LA-MachXO640 devices contain single-ended input buffers and single-ended output buffers with complementary outputs on all the I/O Banks.

LA-MachXO1200 and LA-MachXO2280 devices contain two types of sysIO buffer pairs.

1. Top and Bottom sysIO Buffer Pairs

The sysIO buffer pairs in the top and bottom Banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (for ratioed or absolute input levels). The I/O pairs on the top and bottom of the devices also support differential input buffers. PCI clamps are available on the top Bank I/O buffers. The PCI clamp is enabled after VCC, VCCAUX, and VCCIO are at valid operating levels and the device has been configured.

The two pads in the pair are described as "true" and "comp", where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

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#### 2. Left and Right sysIO Buffer Pairs

The sysIO buffer pairs in the left and right Banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (supporting ratioed and absolute input levels). The devices also have a differential driver per output pair. The referenced input buffer can also be configured as a differential input buffer. In these Banks the two pads in the pair are described as "true" and "comp", where the true pad is associated with the positive side of the differential I/O, and the comp (complementary) pad is associated with the negative side of the differential I/O.

#### Typical I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when  $V_{CC}$  and  $V_{CCAUX}$  have reached satisfactory levels. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user's responsibility to ensure that all  $V_{CCIO}$  Banks are active with valid input logic levels to properly control the output logic states of all the I/O Banks that are critical to the application. The default configuration of the I/O pins in a blank device is tri-state with a weak pull-up to  $V_{CCIO}$ . The I/O pins will maintain the blank configuration until  $V_{CC}$ ,  $V_{CCAUX}$  and  $V_{CCIO}$  have reached satisfactory levels at which time the I/Os will take on the user-configured settings.

The V<sub>CC</sub> and V<sub>CCAUX</sub> supply the power to the FPGA core fabric, whereas the V<sub>CCIO</sub> supplies power to the I/O buffers. In order to simplify system design while providing consistent and predictable I/O behavior, the I/O buffers should be powered up along with the FPGA core fabric. Therefore, V<sub>CCIO</sub> supplies should be powered up before or together with the V<sub>CC</sub> and V<sub>CCAUX</sub> supplies

#### **Supported Standards**

The LA-MachXO sysIO buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS and LVTTL. The buffer supports the LVTTL, LVCMOS 1.2, 1.5, 1.8, 2.5, and 3.3 V standards. In the LVCMOS and LVTTL modes, the buffer has individually configurable options for drive strength, bus maintenance (weak pull-up, weak pull-down, bus-keeper latch or none) and open drain. BLVDS and LVPECL output emulation is supported on all devices. The LA-MachXO1200 and LA-MachXO2280 support on-chip LVDS output buffers on approximately 50% of the I/Os on the left and right Banks. Differential receivers for LVDS, BLVDS and LVPECL are supported on all Banks of LA-MachXO1200 and LA-MachXO2280 devices. PCI support is provided in the top Banks of the LA-MachXO1200 and LA-MachXO2280 devices. Table 3.8. summarizes the I/O characteristics of the devices in the LA-MachXO family.

Table 3.9. and Table 3.10. show the I/O standards (together with their supply and reference voltages) supported by the LA-MachXO devices. For further information on utilizing the sysIO buffer to support a variety of standards please see the details of additional technical documentation at the end of this data sheet.

	LA-MachXO256	LA-MachXO640	LA-MachXO1200	LA-MachXO2280
Number of I/O Banks	2	4	8	8
Type of Input Buffers	Single-ended (all I/O Banks)	Single-ended (all I/O Banks)	Single-ended (all I/O Banks) Differential Receivers (all I/O Banks)	Single-ended (all I/O Banks) Differential Receivers (all I/O Banks)
Types of Output Buffers	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks)	Single-ended buffers with complementary outputs (all I/O Banks) Differential buffers with true LVDS outputs (50% on left and right side)	Single-ended buffers with complementary outputs (all I/O Banks) Differential buffers with true LVDS outputs (50% on left and right side)
Differential Output Emulation Capability	All I/O Banks	All I/O Banks	All I/O Banks	All I/O Banks
PCI Support	No	No	Top side only	Top side only

#### Table 3.8. I/O Support Device by Device

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#### Table 3.9. Supported Input Standards

	VCCIO (Typ.)					
Input Standard	3.3V	2.5V	1.8V	1.5V	1.2V	
Single Ended Interfaces						
LVTTL	$\checkmark$	$\checkmark$				
LVCMOS33	$\checkmark$	$\checkmark$				
LVCMOS25	$\checkmark$	$\checkmark$				
LVCMOS18						
LVCMOS15						
LVCMOS12	$\checkmark$	$\checkmark$				
PCI <sup>1</sup>	$\checkmark$					
Differential Interfaces						
BLVDS <sup>2</sup> , LVDS <sup>2</sup> , LVPECL <sup>2</sup> , RSDS <sup>2</sup>	$\checkmark$	$\checkmark$	$\checkmark$			

Notes:

1. Top Banks of LA-MachXO1200 and LA-MachXO2280 devices only.

2. LA-MachXO1200 and LA-MachXO2280 devices only.

#### Table 3.10. Supported Output Standards

Output Standard	Drive	V <sub>CCIO</sub> (Typ.)
Single-ended Interfaces		
LVTTL	4 mA, 8 mA, 12 mA, 16 mA	3.3
LVCMOS33	4 mA, 8 mA, 12 mA, 14 mA	3.3
LVCMOS25	4 mA, 8 mA, 12 mA, 14 mA	2.5
LVCMOS18	4 mA, 8 mA, 12 mA, 14 mA	1.8
LVCMOS15	4 mA, 8 mA	1.5
LVCMOS12	2 mA, 6 mA	1.2
LVCMOS33, Open Drain	4 mA, 8 mA, 12 mA, 14 mA	—
LVCMOS25, Open Drain	4 mA, 8 mA, 12 mA, 14 mA	—
LVCMOS18, Open Drain	4 mA, 8 mA, 12 mA, 14 mA	—
LVCMOS15, Open Drain	4 mA, 8 mA	_
LVCMOS12, Open Drain	2 mA, 6 mA	—
PCI33 <sup>3</sup>	N/A	3.3
Differential Interfaces		
LVDS <sup>1, 2</sup>	N/A	2.5
BLVDS, RSDS <sup>2</sup>	N/A	2.5
LVPECL <sup>2</sup>	N/A	3.3

Notes:

1. LA-MachXO1200 and LA-MachXO2280 devices have dedicated LVDS buffers.

2. These interfaces can be emulated with external resistors in all devices.

3. Top Banks of LA-MachXO1200 and LA-MachXO2280 devices only.

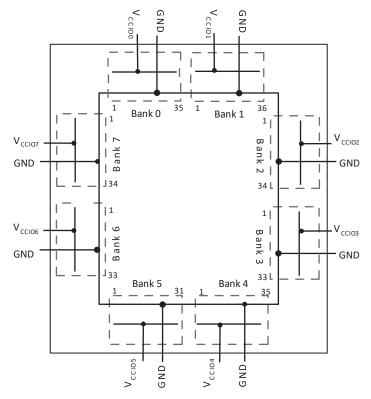
## 3.5.1. sysIO Buffer Banks

The number of Banks vary between the devices of this family. Eight Banks surround the two larger devices, the LAMachXO1200 and LA-MachXO2280 (two Banks per side). The LA-MachXO640 has four Banks (one Bank per side). The smallest member of this family, the LA-MachXO256, has only two Banks.

Each sysIO buffer Bank is capable of supporting multiple I/O standards. Each Bank has its own I/O supply voltage (VCCIO) which allows it to be completely independent from the other Banks. Figure 3.18., Figure 3.19., Figure 3.20. and Figure 3.21. shows the sysIO Banks and their associated supplies for all devices.

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#### Figure 3.18. LA-MachXO2280 Banks

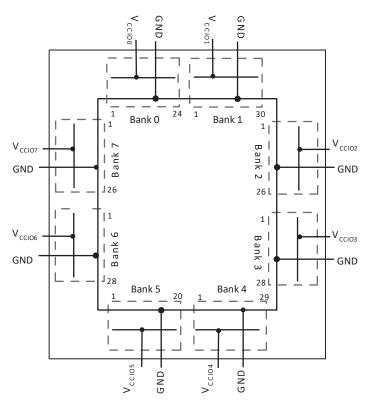


Figure 3.19. LA-MachXO1200 Banks

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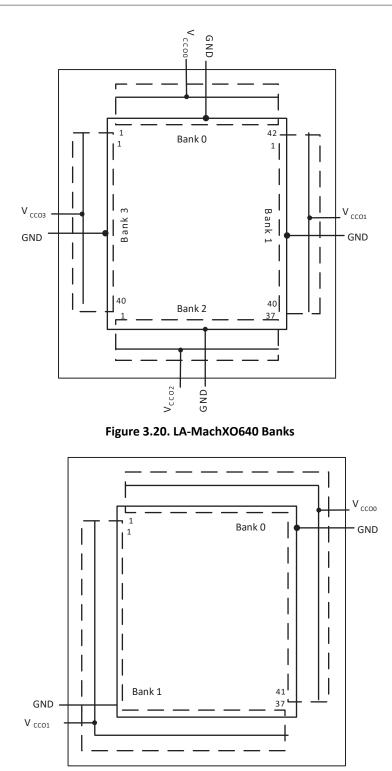


Figure 3.21. LA-MachXO256 Banks

## 3.6. Hot Socketing

The LA-MachXO automotive devices have been carefully designed to ensure predictable behavior during powerup and power-down. Leakage into I/O pins is controlled to within specified limits. This allows for easy integration with the rest of the system. These capabilities make the LA-MachXO ideal for many multiple power supply and hot-swap applications.

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## 3.7. Sleep Mode

The LA-MachXO "C" devices ( $V_{cc} = 1.8/2.5/3.3V$ ) have a sleep mode that allows standby current to be reduced dramatically during periods of system inactivity. Entry and exit to Sleep mode is controlled by the SLEEPN pin.

During Sleep mode, the logic is non-operational, registers and EBR contents are not maintained, and I/Os are tristated. Do not enter Sleep mode during device programming or configuration operation. In Sleep mode, power supplies are in their normal operating range, eliminating the need for external switching of power supplies. Table 3.11. compares the characteristics of Normal, Off and Sleep modes.

Characteristic	Normal	Off	Sleep
SLEEPN Pin	High	-	Low
Static Icc	Typical <10 mA	0	Typical <100 uA
I/O Leakage	<10 µA	<1 mA	<10 µA
Power Supplies VCC/VCCIO/VCCAUX	Normal Range	0	Normal Range
Logic Operation	User Defined	Non Operational	Non operational
I/O Operation	User Defined	Tri-state	Tri-state
JTAG and Programming circuitry	Operational	Non-operational	Non-operational
EBR Contents and Registers	Maintained	Non-maintained	Non-maintained

Table 3.11. Characteristics of Normal, Off and Sleep Modes

## 3.7.1. SLEEPN Pin Characteristics

The SLEEPN pin behaves as an LVCMOS input with the voltage standard appropriate to the VCC supply for the device. This pin also has a weak pull-up, along with a Schmidt trigger and glitch filter to prevent false triggering. An external pull-up to VCC is recommended when Sleep Mode is not used to ensure the device stays in normal operation mode. Typically, the device enters sleep mode several hundred nanoseconds after SLEEPN is held at a valid low and restarts normal operation as specified in the Sleep Mode Timing table. The AC and DC specifications portion of this data sheet shows a detailed timing diagram.

## 3.8. Oscillator

Every LA-MachXO device has an internal CMOS oscillator. The oscillator can be routed as an input clock to the clock tree or to general routing resources. The oscillator frequency can be divided by internal logic. There is a dedicated programming bit to enable/disable the oscillator. The oscillator frequency ranges from 16 MHz to 26 MHz.

## 3.9. Configuration and Testing

The following section describes the configuration and testing features of the LA-MachXO automotive family of devices.

## 3.9.1. IEEE 1149.1-Compliant Boundary Scan Testability

All LA-MachXO devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant test access port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port shares its power supply with one of the VCCIO Banks (LA-MachXO256: V<sub>CCIO1</sub>; LA-MachXO640: V<sub>CCIO2</sub>; LA-MachXO1200 and LAMachXO2280: V<sub>CCIO5</sub>) and can operate with LVCMOS3.3, 2.5, 1.8, 1.5, and 1.2 standards.

For more details on boundary scan test, please see information regarding additional technical documentation at the end of this data sheet.

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## **3.9.2.** Device Configuration

All LA-MachXO devices contain a test access port that can be used for device configuration and programming.

The non-volatile memory in the LA-MachXO can be configured in two different modes:

- In IEEE 1532 mode via the IEEE 1149.1 port. In this mode, the device is off-line and I/Os are controlled by BSCAN registers.
- In background mode via the IEEE 1149.1 port. This allows the device to remain operational in user mode while reprogramming takes place.

The SRAM configuration memory can be configured in three different ways:

- At power-up via the on-chip non-volatile memory.
- After a refresh command is issued via the IEEE 1149.1 port.
- In IEEE 1532 mode via the IEEE 1149.1 port.

Figure 3.22. provides a pictorial representation of the different programming modes available in the LA-MachXO devices. On power-up, the SRAM is ready to be configured with IEEE 1149.1 serial TAP port using IEEE 1532 protocols.

#### Leave Alone I/O

When using IEEE 1532 mode for non-volatile memory programming, SRAM configuration, or issuing a refresh command, users may specify I/Os as high, low, tristated or held at current value. This provides excellent flexibility for implementing systems where reconfiguration or reprogramming occurs on-the-fly.

#### TransFR (Transparent Field Reconfiguration)

TransFR (TFR) is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a single ispVM command. See Lattice technical note #TN1087, Minimizing System Interruption During Configuration Using TransFR Technology, for details.

#### Security

The LA-MachXO automotive devices contain security bits that, when set, prevent the readback of the SRAM configuration and non-volatile memory spaces. Once set, the only way to clear the security bits is to erase the memory space.

For more information on device configuration, please see details of additional technical documentation at the end of this data sheet.

### 3.9.3. AEC-Q100 Tested and Qualified

The Automotive Electronics Council (AEC) consists of two committees: the Quality Systems Committee and the Component Technical Committee. These committees are composed of representatives from sustaining and other associate members. The AEC Component Technical Committee is the standardization body for establishing standards for reliable, high quality electronic components. In particular, the AEC-Q100 specification "Stress Test for Qualification for Integrated Circuits" defines qualification and re-qualification requirements for electronic components. Components meeting these specifications are suitable for use in the harsh automotive environment without additional component-level qualification testing. Lattice's LA-ispMACH 4000V and LA-MachXO devices completed and passed the requirements of the AEC-Q100 specification.



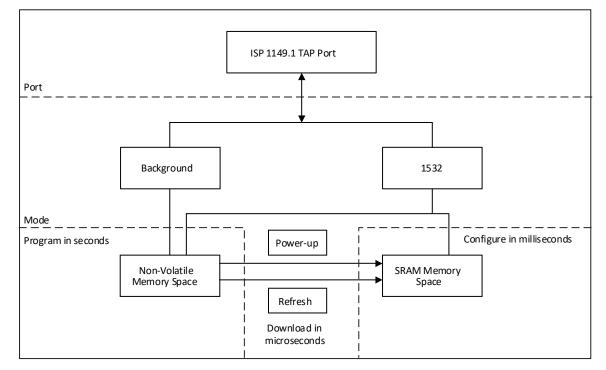


Figure 3.22. LA-MachXO Configuration and Programming

## 3.9.4. Density Shifting

The LA-MachXO family has been designed to enable density migration in the same package. Furthermore, the architecture ensures a high success rate when performing design migration from lower density parts to higher density parts. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case.

## 3.10. DC and Switching Characteristics

## 3.10.1. Absolute Maximum Ratings<sup>1, 2, 3</sup>

	LCMXO E (1.2V)	LCMXO C (1.8V/2.5V/3.3V)
Supply Voltage VCC	0.5 to 1.32V	0.5 to 3.75V
Supply Voltage VCCAUX	0.5 to 3.75V	0.5 to 3.75V
Output Supply Voltage VCCIO	0.5 to 3.75V	0.5 to 3.75V
I/O Tristate Voltage Applied 4	0.5 to 3.75V	0.5 to 3.75V
Dedicated Input Voltage Applied4	0.5 to 3.75V	0.5 to 4.25V
Storage Temperature (ambient)	65 to 150°C	65 to 150°C
Junction Temp. (Tj)	+125°C	+125°C
Notes:		

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

2. Compliance with the Lattice Thermal Management document is required.

- 3. All voltages referenced to GND.
- 4. Overshoot and undershoot of -2V to (VIHMAX + 2) volts is permitted for a duration of <20ns.



### 3.10.2. Recommended Operating Conditions<sup>1</sup>

Symbol	Parameter	Min.	Max.	Units
VCC	Core Supply Voltage for 1.2 V Devices		1.26	V
	Core Supply Voltage for 1.8 V/2.5 V/3.3 V Devices		3.465	V
VCCAUX3	Auxiliary Supply Voltage	3.135	3.465	V
VCCIO2	I/O Driver Supply Voltage		3.465	V
tJAUTO	Junction Temperature Automotive Operation	-40	125	oC
tJFLASHAUTO	Junction Temperature, Flash Programming, Automotive	-40	125	oC

Notes:

Like power supplies must be tied together. For example, if V<sub>CCIO</sub> and V<sub>CC</sub> are both 2.5 V, they must also be the same supply. 3.3 V V<sub>CCIO</sub> and 1.2 V V<sub>CCIO</sub> should be tied to V<sub>CCAUX</sub> or 1.2 V V<sub>CC</sub> respectively.

- 2. See recommended voltages by I/O standard in subsequent table.
- 3.  $V_{CC}$  must reach minimum  $V_{CC}$  value before  $V_{CCAUX}$  reaches 2.5 V.

## 3.10.3. LA-MachXO256 and LA-MachXO640 Hot Socketing Specifications<sup>1, 2, 3</sup>

Symbol	Parameter	Condition	Min.	Тур.	Max	Units
IDK	Input or I/O leakage Current	$0 \le V_{IN} \le V_{IH}$ (MAX)	-	—	+/-1000	μΑ

Notes:

1. Insensitive to sequence of V<sub>CC</sub>, V<sub>CCAUX</sub>, and V<sub>CCI0</sub>. However, assumes monotonic rise/fall rates for V<sub>CC</sub>, V<sub>CCAUX</sub>, and V<sub>CCI0</sub>.

2.  $0 \le V_{CC} \le V_{CC}$  (MAX),  $0 \le V_{CCIO} \le V_{CCIO}$  (MAX) and  $0 \le V_{CCAUX} \le V_{CCAUX}$  (MAX).

3.  $I_{DK}$  is additive to  $I_{PU}$ ,  $I_{PD}$  or  $I_{BH}$ .

## 3.10.4. LA-MachXO1200 and LA-MachXO2280 Hot Socketing Specifications<sup>1, 2, 3, 4</sup>

	61					
Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
Non-LVDS Ge	Non-LVDS General Purpose syslOs					
IDK	Input or I/O Leakage Current	$0 \le V_{IN} \le V_{IH}$ (MAX.)	-	—	+/-1000	μA
LVDS Genera	l Purpose syslOs					
<sup>I</sup> DK_LVDS	Input or I/O Leakage Current	$V_{IN} \leq V_{CCIO}$	-	—	+/-1000	μΑ
		V <sub>IN</sub> > V <sub>CCIO</sub>	-	35	—	mA

Notes:

1. Insensitive to sequence of V<sub>CC</sub>, V<sub>CCAUX</sub>, and V<sub>CCIO</sub>. However, assumes monotonic rise/fall rates for V<sub>CC</sub>, V<sub>CCAUX</sub>, and V<sub>CCIO</sub>.

2.  $0 \le V_{CC} \le V_{CC}$  (MAX),  $0 \le V_{CCIO} \le V_{CCIO}$  (MAX), and  $0 \le V_{CCAUX} \le V_{CCAUX}$  (MAX).

3.  $I_{DK}$  is additive to  $I_{PU}$ ,  $I_{PW}$  or  $I_{BH}$ .

4. LVCMOS and LVTTL only.



3.10.5. DC Electrical Characteristics Over Recommended Operating Conditions				
		Developmenter		

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
1, 4, 5 I <sub>IL,</sub> I <sub>IH</sub>	Input or I/O Leakage	$0 \leq V_{IN} \leq (V_{CCIO} - 0.2V)$	—	_	10	μΑ
,		$(V_{CCIO} - 0.2V) < V_{IN} \le 3.6V$	_	_	40	μA
I <sub>PU</sub>	I/O Active Pull-up Current	$0 \leq V_{IN} \leq 0.7 \; V_{CCIO}$	-30	_	-150	μΑ
I <sub>PD</sub>	I/O Active Pull-down Current	$V_{IL}$ (MAX) $\leq V_{IN} \leq V_{IH}$ (MAX)	30	_	150	μΑ
I <sub>BHLS</sub>	Bus Hold Low sustaining current	V <sub>IN</sub> = V <sub>IL</sub> (MAX)	30	_	—	μA
I <sub>BHHS</sub>	Bus Hold High sustaining current	V <sub>IN</sub> = 0.7V <sub>CCIO</sub>	-30	_	—	μA
I <sub>BHLO</sub>	Bus Hold Low Overdrive current	$0 \le V_{IN} \le V_{IH}$ (MAX)	—	_	150	μΑ
I <sub>BHHO</sub>	Bus Hold High Overdrive current	$0 \le V_{IN} \le V_{IH}$ (MAX)	_	_	-150	μΑ
V <sub>BHT</sub> <sup>3</sup>	Bus Hold trip Points	$0 \le V_{IN} \le V_{IH}$ (MAX)	V <sub>IL</sub> (MAX)	_	V <sub>IH</sub> (MIN)	V
C1	I/O Capacitance <sup>2</sup>	V <sub>CCIO</sub> = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V <sub>CC</sub> = Typ., V <sub>IO</sub> = 0 to V <sub>IH</sub> (MAX)	_	8	—	pf
C2	Dedicated Input Capacitance <sup>2</sup>	V <sub>CCIO</sub> = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V <sub>CC</sub> = Typ., V <sub>IO</sub> = 0 to V <sub>IH</sub> (MAX)	_	8	—	pf

#### Notes:

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

- 2. T<sub>A</sub> 25°C, f = 1.0 MHz
- 3. Please refer to  $V_{IL}$  and  $V_{IH}$  in the sysIO Single-Ended DC Electrical Characteristics table of this document.
- 4. Not applicable to SLEEPN pin.
- When V<sub>IH</sub> is higher than V<sub>CCIO</sub>, a transient current typically of 30 ns in duration or less with a peak current of 6 mA can occur on the high-tolow transition. For LA-MachXO1200 and LA-MachXO2280 true LVDS output pins, V<sub>IH</sub> must be less than or equal to V<sub>CCIO</sub>.

### 3.10.6. Supply Current (Sleep Mode)<sup>1, 2</sup>

Symbol	Parameter	Device	Typ. <sup>3</sup>	Max.	Units
ICC	Core Power Supply	LCMXO256C	12	25	μA
		LCMXO640C	12	25	μΑ
ICCAUX	Auxiliary Power Supply	LCMXO256C	1	15	μA
		LCMXO640C	1	25	μA
ICCIO	Bank Power Supply <sup>4</sup>	All LCMXO 'C' Devices	2	30	μΑ

#### Notes:

1. Assumes all inputs are configured as LVCMOS and held at the VCCIO or GND.

- 2. Frequency = 0 MHz.
- 3.  $T_A = 25^{\circ}C$ , power supplies at nominal voltage.
- 4. Per Bank.

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## 3.10.7. Supply Current (Standby)<sup>1, 2, 3, 4</sup>

#### **Over Recommended Operating Conditions**

Symbol	Parameter	Device	Typ.⁵	Units
ICC	Core Power Supply	LCMXO256C	7	mA
		LCMXO640C	9	mA
		LCMXO256E	4	mA
		LCMXO640E	6	mA
		LCMXO1200E	10	mA
		LCMXO2280E	12	mA
ICCAUX	Auxiliary Power Supply V <sub>CCAUX</sub> =	LCMXO256E/C	5	mA
	3.3V	LCMXO640E/C	7	mA
		LCMXO1200E	12	mA
		LCMXO2280E	13	mA
Iccio	Bank Power Supply <sup>6</sup>	All devices	2	mA

Notes:

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.

2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at V<sub>CCIO</sub> or GND.

3. Frequency = 0 MHz.

- 4. User pattern = blank.
- 5.  $T_J = 25^{\circ}$ C, power supplies at nominal voltage.
- 6. Per Bank. V<sub>CCIO</sub> = 2.5 V. Does not include pull-up/pull-down

## 3.10.8. Initialization Supply Current<sup>1, 2, 3, 4</sup>

#### **Over Recommended Operating Conditions**

Symbol	Parameter	Device	Typ.⁵	Units
ICC	Core Power Supply	LCMXO256C	13	mA
		LCMXO640C	17	mA
		LCMXO256E	10	mA
		LCMXO640E	14	mA
		LCMXO1200E	18	mA
		LCMXO2280E	20	mA
ICCAUX	Auxiliary Power Supply V <sub>CCAUX</sub> =	LCMXO256E/C	10	mA
	3.3V	LCMXO640E/C	13	mA
		LCMXO1200E	24	mA
		LCMXO2280E	25	mA
ICCIO	Bank Power Supply <sup>6</sup>	All devices	2	mA

Notes:

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.

- 2. Assumes all I/O pins are held at  $V_{CCIO}$  or GND.
- 3. Frequency = 0 MHz.
- 4. Typical user pattern.
- 5.  $T_J = 250C$ , power supplies at nominal voltage.
- 6. Per Bank,  $V_{CCIO}$  = 2.5 V. Does not include pull-up/pull-down



## 3.10.9. Programming and Erase Flash Supply Current<sup>1, 2, 3, 4</sup>

Symbol	Parameter	Device	Typ.⁵	Units
Icc	Core Power Supply	LCMXO256C	9	mA
		LCMXO640C	11	mA
		LCMXO256E	6	mA
		LCMXO640E	8	mA
		LCMXO1200E	12	mA
		LCMXO2280E	14	mA
ICCAUX	Auxiliary Power Supply	LCMXO256E/C	8	mA
	V <sub>CCAUX</sub> = 3.3V	LCMXO640E/C	10	mA
		LCMXO1200E	15	mA
		LCMXO2280E	16	mA
ICCIO	Bank Power Supply <sup>6</sup>	All devices	2	mA

Notes:

1. For further information on supply current, please see details of additional technical documentation at the end of this data sheet.

- 2. Assumes all I/O pins are held at V<sub>CCIO</sub> or GND.
- 3. Typical user pattern.
- 4. JTAG programming is at 25 MHz.
- 5.  $T_J = 25^{\circ}C$ , power supplies at nominal voltage.
- 6. Per Bank.  $V_{CCIO}$  = 2.5 V. Does not include pull-up/pull-down.

### 3.10.10. sysIO Recommended Operating Conditions

Standard	V <sub>CCI0</sub> (V)					
	Min.	Тур.	Max.			
LVCMOS 3.3	3.135	3.3	3.465			
LVCMOS 2.5	2.375	2.5	2.625			
LVCMOS 1.8	1.71	1.8	1.89			
LVCMOS 1.5	1.425	1.5	1.575			
LVCMOS 1.2	1.14	1.2	1.26			
LVTTL	3.135	3.3	3.465			
PCI <sup>3</sup>	3.135	3.3	3.465			
LVDS <sup>1, 2</sup>	2.375	2.5	2.625			
LVPECL <sup>1</sup>	3.135	3.3	3.465			
BLVDS <sup>1</sup>	2.375	2.5	2.625			
RSDS <sup>1</sup>	2.375	2.5	2.625			

Notes:

1. Inputs on chip. Outputs are implemented with the addition of external resistors.

2. MachXO1200 and MachXO2280 devices have dedicated LVDS buffers

3. Input on the top bank of the MachXO1200 and MachXO2280 only.

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Input/Output		V <sub>IL</sub>	V <sub>IH</sub>		V <sub>OL</sub>	V <sub>OH</sub> Min.	lol <sup>1</sup> (mA)	l <sub>он</sub> 1(mA)
Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	Max. (V)	(V)		
LVCMOS 3.3	-0.3	0.8	2.0	3.6	0.4	V <sub>CCIO</sub> - 0.4	16, 12, 8, 4	-14, -12, -8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVTTL	-0.3	0.8	2.0	3.6	0.4	2.4	16	-16
					0.4	V <sub>CCIO</sub> - 0.4	12, 8, 4	-12, -8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	V <sub>CCIO</sub> - 0.4	16, 12, 8, 4	-14, -12, -8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS 1.8	-0.3	0.35V <sub>CCIO</sub>	0.65V <sub>CCIO</sub>	3.6	0.4	V <sub>CCIO</sub> - 0.4	16, 12, 8, 4	-14, -12, -8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS 1.5	-0.3	0.35V <sub>CCIO</sub>	0.65V <sub>CCIO</sub>	3.6	0.4	V <sub>CCIO</sub> - 0.4	8, 4	-8, -4
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS 1.2	-0.3	0.42	0.78	3.6	0.4	V <sub>CCIO</sub> - 0.4	6, 2	-6, -2
("C" Version)					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
LVCMOS 1.2	-0.3	0.35V <sub>CC</sub>	0.65V <sub>CC</sub>	3.6	0.4	V <sub>CCIO</sub> - 0.4	6, 2	-6, -2
("E" Version)					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1
PCI	-0.3	0.3V <sub>CCIO</sub>	0.5V <sub>CCIO</sub>	3.6	0.1V <sub>CCIO</sub>	0.9V <sub>CCIO</sub>	1.5	-0.5

3.10.11.	sysIO Single-Ended DC Electrical Characteristics
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**Note:** The average DC current drawn by I/Os between GND connections, or between the last GND in an I/O Bank and the end of an I/O Bank, as shown in the logic signal connections table shall not exceed n \* 8 mA. Where n is the number of I/Os between Bank GND connections or between the last GND in a Bank and the end of a Bank.

## **3.11.** sysIO Differential Electrical Characteristics

## 3.11.1. LVDS

**Over Recommended Operating Conditions** 

Parameter	Parameter Description	Test Conditions	Min.	Тур.	Max.	Units
Symbol						
V <sub>INP</sub> , V <sub>INM</sub>	Input Voltage		0	-	2.4	V
V <sub>THD</sub>	Differential Input Threshold		+/-100	_	-	mV
V <sub>CM</sub>	Input Common Mode Voltage	$100mV \le V_{THD}$	V <sub>THD</sub> /2	1.2	1.8	V
		$200mV \le V_{THD}$	V <sub>THD</sub> /2	1.2	1.9	V
		$350mV \le V_{THD}$	V <sub>THD</sub> /2	1.2	2.0	V
IIN	Input current	Power on	-	_	+/-10	μΑ
V <sub>OH</sub>	Output high voltage for $V_{OP}$ or $V_{OM}$	R <sub>T</sub> = 100 Ohm	_	1.38	1.60	V
V <sub>OL</sub>	Output low voltage for $V_{OP}$ or $V_{OM}$	R <sub>T</sub> = 100 Ohm	0.9V	1.03	-	V
V <sub>OD</sub>	Output voltage differential	(V <sub>OP</sub> - V <sub>OM</sub> ), R <sub>T</sub> = 100 Ohm	250	350	450	mV
ΔV <sub>OD</sub>	Change in V <sub>OD</sub> between high and low		_	_	50	mV
V <sub>OS</sub>	Output voltage offset	(V <sub>OP</sub> - V <sub>OM</sub> )/2, R <sub>T</sub> = 100 Ohm	1.125	1.25	1.375	V
ΔV <sub>OS</sub>	Change in V <sub>OS</sub> between H and L		-	—	50	mV
IOSD	Output short circuit current	V <sub>OD</sub> = 0V Driver outputs shorted	-	—	6	mA

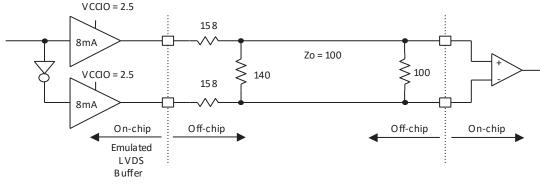
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## 3.11.2. LVDS Emulation

LA-MachXO automotive devices can support LVDS outputs via emulation (LVDS25E), in addition to the LVDS support that is available on-chip on certain devices. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3.23. is one possible solution for LVDS standard implementation. Resistor values in Figure 3.23. are industry standard values for 1% resistors.



Note: All resistors are  $\pm 1\%$ .

#### Figure 3.23. LVDS Using External Resistors (LVDS25E)

The LVDS differential input buffers are available on certain devices in the LA-MachXO family.

Over Recommended Operating Conditions				
Parameter	Description	Typical	Units	
Z <sub>OUT</sub>	Output impedance	20	^	
RS	Driver series resistor	294	^	
Rp	Driver parallel resistor	121	Λ	
RT	Receiver termination	100	^	
VOH	Output high voltage	1.43	V	
V <sub>OL</sub>	Output low voltage	1.07	V	
V <sub>OD</sub>	Output differential voltage	0.35	V	
V <sub>CM</sub>	Output common mode voltage	1.25	V	
ZBACK	Back impedance	100	^	
IDC	DC output current	3.66	mA	

#### Table 3.12. LVDS DC Conditions

### 3.11.3. BLVDS

The LA-MachXO automotive family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. The input standard is supported by the LVDS differential input buffer on certain devices. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3.24. is one possible solution for bi-directional multi-point differential signals.

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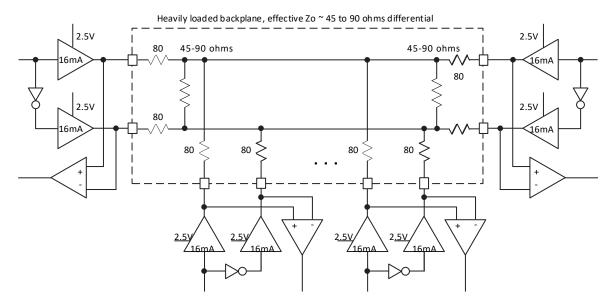


Figure 3.24. BLVDS Multi-point Output Example

#### Table 3.13. BLVDS DC Conditions<sup>1</sup>

Over Recommended	Operating Conditions
over necconniciaca	operating contactions

Symbol	Description	Nominal		Units
		Zo = 45	Zo = 90	
ZOUT	Output impedance	100	100	ohm
R <sub>TLEFT</sub>	Left end termination	45	90	ohm
RTRIGHT	Right end termination	45	90	ohm
V <sub>OH</sub>	Output high voltage	1.375	1.48	V
V <sub>OL</sub>	Output low voltage	1.125	1.02	V
V <sub>OD</sub>	Output differential voltage	0.25	0.46	V
V <sub>CM</sub>	Output common mode voltage	1.25	1.25	V
IDC	DC output current	11.2	10.2	mA

#### 3.11.4. LVPECL

The LA-MachXO automotive family supports the differential LVPECL standard through emulation. This output standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs on all the devices. The LVPECL input standard is supported by the LVDS differential input buffer on certain devices. The scheme shown in Figure 3.25. is one possible solution for point-to-point signals.

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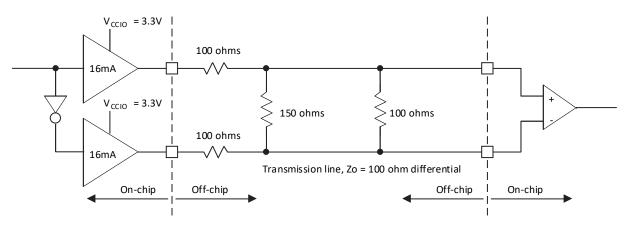


Figure 3.25. Differential LVPECL

#### Table 3.14. LVPECL DC Conditions<sup>1</sup>

Symbol	Description	Nominal	Units
Z <sub>OUT</sub>	Output impedance	100	ohm
Rp	Driver parallel resistor	150	ohm
RT	Receiver termination	100	ohm
V <sub>OH</sub>	Output high voltage	2.03	V
V <sub>OL</sub>	Output low voltage	1.27	V
V <sub>OD</sub>	Output differential voltage	0.76	V
VCM	Output common mode voltage	1.65	V
ZBACK	Back impedance	85.7	ohm
IDC	DC output current	12.7	mA

Note: For input buffer, see LVDS table.

For further information on LVPECL, BLVDS and other differential interfaces please see details of additional technical documentation at the end of the data sheet.

#### 3.11.5. RSDS

The LA-MachXO automotive family supports the differential RSDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs on all the devices. The RSDS input standard is supported by the LVDS differential input buffer on certain devices. The scheme shown in Figure 3.26. is one possible solution for RSDS standard implementation. Use LVDS25E mode with suggested resistors for RSDS operation. Resistor values in Figure 3.26. are industry standard values for 1% resistors.



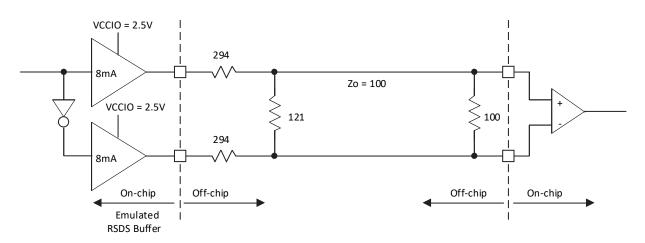


Figure 3.26. RSDS (Reduced Swing Differential Standard)

### Table 3.15. RSDS DC Conditions

Parameter	Description	Typical	Units
Z <sub>OUT</sub>	Output impedance	20	ohm
RS	Driver series resistor	294	ohm
Rp	Driver parallel resistor	121	ohm
RŢ	Receiver termination	100	ohm
VOH	Output high voltage	1.35	V
V <sub>OL</sub>	Output low voltage	1.15	V
V <sub>OD</sub>	Output differential voltage	0.20	V
VCM	Output common mode voltage	1.25	V
ZBACK	Back impedance	101.5	ohm
IDC	DC output current	3.66	mA

### **3.12.** Typical Building Block Function Performance<sup>1</sup>

### Pin-to-Pin Performance (LVCMOS25 12mA Drive)

Function	-3 Timing	Units		
Basic Functions				
16-bit decoder	9.4	ns		
4:1 MUX	6.3	ns		
16:1 MUX	7.1	ns		

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Function	-3 Timing	Units
Basic Functions		
16:1 MUX	348	MHz
16-bit adder	209	MHz
16-bit counter	277	MHz
64-bit counter	143	MHz
Embedded Memory Functions (1200 and 228	30 Devices Only)	
256x36 Single Port RAM	203	MHz
512x18 True-Dual Port RAM	203	MHz
Distributed Memory Functions		
16x2 Single Port RAM	310	MHz
64x2 Single Port RAM	229	MHz
128x4 Single Port RAM	186	MHz
32x2 Pseudo-Dual Port RAM	224	MHz
64x4 Pseudo-Dual Port RAM	194	MHz

### 3.12.1. Register-to-Register Performance

**Note:** The above timing numbers are generated using the ispLEVER design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device. Rev. A 0.19

### 3.13. Derating Logic Timing

Logic Timing provided in the following sections of the data sheet and the ispLEVER design tools are worst case numbers in the operating range. Actual delays may be much faster. The ispLEVER design tool from Lattice can provide logic timing numbers at a particular temperature and voltage.



## **3.14.** LA-MachXO External Switching Characteristics<sup>1</sup>

**Over Recommended Operating Conditions** 

Parameter	Description	Device	-	3	Units
			Min.	Max.	
General I/O Pin	Parameters (Using Global Clock without PLL) <sup>1</sup>				
t <sub>PD</sub>	Best Case tPD Through 1 LUT	LCMXO256	_	4.9	ns
		LCMXO640	_	4.9	ns
		LCMXO1200	_	5.1	ns
		LCMXO2280	_	5.1	ns
tco	Best Case Clock to Output - From PFU	LCMXO256	_	5.6	ns
		LCMXO640	_	5.7	ns
		LCMXO1200	_	6.1	ns
		LCMXO2280	_	6.1	ns
t <sub>SU</sub>	Clock to Data Setup - To PFU	LCMXO256	1.8	_	ns
		LCMXO640	1.5	_	ns
		LCMXO1200	1.6	_	ns
		LCMXO2280	1.5	_	ns
tн	Clock to Data Hold - To PFU	LCMXO256	-0.3	_	ns
		LCMXO640	-0.1	_	ns
		LCMXO1200	0.0	_	ns
		LCMXO2280	-0.4	_	ns
fMAX_IO	Clock Frequency of I/O and PFU Register	LCMXO256	_	500	MHz
—		LCMXO640	_	500	MHz
		LCMXO1200	_	500	MHz
		LCMXO2280	_	500	MHz
<sup>t</sup> SKEW_PRI	Global Clock Skew Across Device	LCMXO256	_	240	ps
—		LCMXO640	_	240	ps
		LCMXO1200	_	260	ps
		LCMXO2280	_	260	ps

Note: General timing numbers based on LVCMOS2.5V, 12 mA. Rev. A 0.19

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## **3.15.** LA-MachXO Internal Timing Parameters<sup>1</sup>

**Over Recommended Operating Conditions** 

Parameter	Description	-3		Units	
		Min.	Max.		
PFU/PFF Logic Mo	de Timing	1			
<sup>t</sup> LUT4_PFU	LUT4 delay (A to D inputs to F output)		0.39	ns	
<sup>t</sup> LUT6_PFU	LUT6 delay (A to D inputs to OFX output)	—	0.62	ns	
tLSR_PFU	Set/Reset to output of PFU	-	1.26	ns	
tsum_pfu	Clock to Mux (M0,M1) input setup time	0.15	-	ns	
<sup>t</sup> HM_PFU	Clock to Mux (M0,M1) input hold time	-0.07	-	ns	
tsud_pfu	Clock to D input setup time	0.18	_	ns	
<sup>t</sup> HD_PFU	Clock to D input hold time	-0.04	—	ns	
<sup>t</sup> CK2Q_PFU	Clock to Q delay, D-type register configuration	_	0.56	ns	
tLE2Q_PFU	Clock to Q delay latch configuration	—	0.74	ns	
t <sub>LD2Q_PFU</sub>	D to Q throughput delay when latch is enabled	—	0.77	ns	
PFU Dual Port Me	mory Mode Timing	I.	1		
<sup>t</sup> CORAM_PFU	Clock to Output	_	0.56	ns	
<sup>t</sup> SUDATA_PFU	Data Setup Time	-0.25	_	ns	
<sup>t</sup> HDATA_PFU	Data Hold Time	0.39	—	ns	
<sup>t</sup> SUADDR_PFU	Address Setup Time	-0.65	—	ns	
tHADDR_PFU	Address Hold Time	0.99	-	ns	
<sup>t</sup> SUWREN_PFU	Write/Read Enable Setup Time	-0.30	—	ns	
thwren pfu	Write/Read Enable Hold Time	0.47	-	ns	
PIO Input/Output	Buffer Timing	I.	1		
<sup>t</sup> IN_PIO	Input Buffer Delay	—	1.06	ns	
<sup>t</sup> out_pio	Output Buffer Delay	—	1.80	ns	
EBR Timing (1200	and 2280 Devices Only)				
<sup>t</sup> CO_EBR	Clock to output from Address or Data with no output register	—	3.14	ns	
<sup>t</sup> coo_ebr	Clock to output from EBR output Register	-	0.75	ns	
<sup>t</sup> SUDATA_EBR	Setup Data to EBR Memory	-0.37	—	ns	
<sup>t</sup> HDATA_EBR	Hold Data to EBR Memory	0.57	—	ns	
<sup>t</sup> SUADDR_EBR	Setup Address to EBR Memory	-0.37	—	ns	
<sup>t</sup> HADDR_EBR	Hold Address to EBR Memory	0.57	—	ns	
<sup>t</sup> SUWREN_EBR	Setup Write/Read Enable to EBR Memory	-0.23	—	ns	
<sup>t</sup> HWREN_EBR	Hold Write/Read Enable to EBR Memory	0.36	—	ns	
tSUCE_EBR	Clock Enable Setup Time to EBR Output Register	0.27	-	ns	
thce_ebr	Clock Enable Hold Time to EBR Output Register	-0.18	-	ns	
t <sub>rsto</sub> ebr	Reset To Output Delay Time from EBR Output Regis- ter	-	1.44	ns	
—	200 and 2280 Devices Only)	1	1	I	
<sup>t</sup> RSTREC	Reset Recovery to Rising Clock	-	1.00	ns	
t <sub>RSTSU</sub>	Reset Signal Setup Time	1.00	—	ns	

Note: Internal parameters are characterized but not tested on every device. Rev. A 0.19

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# 3.16. LA-MachXO Family Timing Adders<sup>1, 2, 3</sup>

#### Over Recommended Operating Conditions

Buffer Type	Description	-3	Units
Input Adjusters	·		
LVDS25 <sup>4</sup>	LVDS	0.61	ns
BLVDS25 <sup>4</sup>	BLVDS	0.61	ns
LVPECL33 <sup>4</sup>	LVPECL	0.59	ns
LVTTL33	LVTTL	0.01	ns
LVCMOS33	LVCMOS 3.3	0.01	ns
LVCMOS25	LVCMOS 2.5	0.00	ns
LVCMOS18	LVCMOS 1.8	0.10	ns
LVCMOS15	LVCMOS 1.5	0.19	ns
LVCMOS12	LVCMOS 1.2	0.56	ns
PCI33 <sup>4</sup>	PCI	0.01	ns
Output Adjusters		•	
LVDS25E	LVDS 2.5 E	-0.18	ns
LVDS25 <sup>4</sup>	LVDS 2.5	-0.30	ns
BLVDS25	BLVDS 2.5	-0.04	ns
LVPECL33	LVPECL 3.3	0.05	ns
LVTTL33_4mA	LVTTL 4mA drive	0.05	ns
LVTTL33_8mA	LVTTL 8mA drive	0.08	ns
LVTTL33_12mA	LVTTL 12mA drive	-0.01	ns
LVTTL33_16mA	LVTTL 16mA drive	0.70	ns
LVCMOS33_4mA	LVCMOS 3.3 4mA drive	0.05	ns
LVCMOS33_8mA	LVCMOS 3.3 8mA drive	0.08	ns
LVCMOS33_12mA	LVCMOS 3.3 12mA drive	-0.01	ns
LVCMOS33_14mA	LVCMOS 3.3 14mA drive	0.70	ns
LVCMOS25_4mA	LVCMOS 2.5 4mA drive	0.07	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive	0.13	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive	0.00	ns
LVCMOS25_14mA	LVCMOS 2.5 14mA drive	0.47	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive	0.15	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive	0.06	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive	-0.08	ns
LVCMOS18_14mA	LVCMOS 1.8 14mA drive	0.09	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive	0.22	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive	0.07	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive	0.36	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive	0.07	ns
PCI33 <sup>4</sup>	PCI33	2.59	ns

#### Notes:

1. Timing adders are characterized but not tested on every device.

2. LVCMOS timing is measured with the load specified in Switching Test Conditions table.

- 3. All other standards tested according to the appropriate specifications.
- I/O standard only available in LCMXO1200 and LCMXO2280 devices. Rev. A 0.19

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## 3.17. sysCLOCK PLL Timing

**Over Recommended Operating Conditions** 

Parameter	Descriptions	Conditions	Min.	Max.	Units
fIN	Input Clock Frequency (CLKI, CLKFB)		25	420	MHz
<sup>f</sup> оuт	Output Clock Frequency (CLKOP, CLKOS)		25	420	MHz
fout2	K-Divider Output Frequency (CLKOK)		0.195	210	MHz
fvco	PLL VCO Frequency		420	840	MHz
fpfd	Phase Detector Input Frequency		25	_	MHz
	AC Characteristics				
t <sub>DT</sub>	Output Clock Duty Cycle	Default duty cycle selected <sup>3</sup>	45	55	%
tPH⁴	Output Phase Accuracy		_	0.05	UI
<sup>t</sup> OPJIT <sup>1</sup>	Output Clock Period Jitter	Fout $\geq$ 100MHz	-	+/-120	ps
		Fout < 100MHz	—	0.02	UIPP
t <sub>SK</sub>	Input Clock to Output Clock Skew	Divider ratio = integer	—	+/-200	ps
tw	Output Clock Pulse Width	At 90% or 10% <sup>3</sup>	1	—	ns
<sup>t</sup> LOCK <sup>2</sup>	PLL Lock-in Time		_	150	μs
tpA	Programmable Delay Unit		100	450	ps
t <sub>ipjit</sub>	Input Clock Period Jitter		-	+/-200	ps
t <sub>FBKDLY</sub>	External Feedback Delay		-	10	ns
tнı	Input Clock High Time	90% to 90%	0.5	-	ns
t <sub>LO</sub>	Input Clock Low Time	10% to 10%	0.5	—	ns
t <sub>RST</sub>	RST Pulse Width		10	—	ns

Notes:

1. Jitter sample is taken over 10,000 samples of the primary PLL output with a clean reference clock.

2. Output clock is valid after tLOCK for PLL reset and dynamic delay adjustment.

3. Using LVDS output buffers.

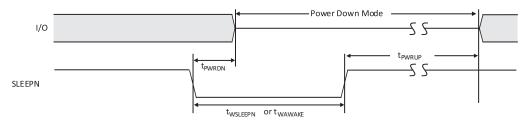
4. CLKOS as compared to CLKOP output.

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## 3.18. LA-MachXO "C" Sleep Mode Timing

Symbol	Parameter	Device	Min.	Тур.	Max	Units
tpwrdn	SLEEPN Low to Power Down	All	—	-	400	ns
t <sub>PWRUP</sub>	SLEEPN High to Power Up	LCMXO256	_	-	400	μs
		LCMXO640	_		600	μs
twsleepn	SLEEPN Pulse Width	All	400	-		ns
<sup>t</sup> WAWAKE	SLEEPN Pulse Rejection	All	_		100	ns

Note: Rev. A 0.19







### 3.19. Flash Download Time

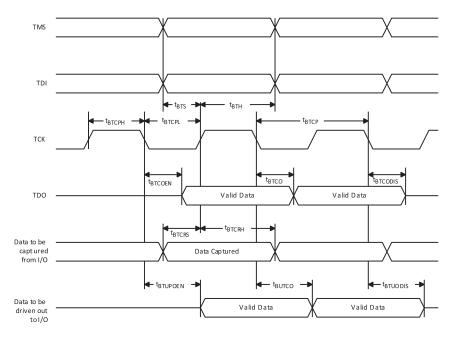
Symbol	Parameter		Min.	Тур.	Max.	Units
t <sub>REFRESH</sub>	Minimum V <sub>CC</sub> or	LCMXO256			0.4	ms
	V <sub>CCAUX</sub> (later of the two	LCMXO640	—	—	0.6	ms
	supplies) to Device I/O	LCMXO1200	_	_	0.8	ms
	Active	LCMXO2280	-	_	1.0	ms

## 3.20. JTAG Port Timing Specifications

**Over Recommended Operating Conditions** 

Symbol	Parameter	Min.	Max.	Units
fMAX	TCK [BSCAN] clock frequency	—	25	MHz
t <sub>BTCP</sub>	TCK [BSCAN] clock pulse width	40	—	ns
<sup>t</sup> втсрн	TCK [BSCAN] clock pulse width high	20	—	ns
<sup>t</sup> BTCPL	TCK [BSCAN] clock pulse width low	20	—	ns
t <sub>BTS</sub>	TCK [BSCAN] setup time	8	—	ns
<sup>t</sup> втн	TCK [BSCAN] hold time	10	_	ns
t <sub>BTRF</sub>	TCK [BSCAN] rise/fall time	50	—	mV/ns
<sup>t</sup> втсо	TAP controller falling edge of clock to output valid	_	10	ns
<sup>t</sup> BTCODIS	TAP controller falling edge of clock to output disabled	_	10	ns
<sup>t</sup> BTCOEN	TAP controller falling edge of clock to output enabled	—	10	ns
<sup>t</sup> BTCRS	BSCAN test capture register setup time	8	—	ns
<sup>t</sup> BTCRH	BSCAN test capture register hold time	25	—	ns
<sup>t</sup> BUTCO	BSCAN test update register, falling edge of clock to output valid	—	25	ns
<sup>t</sup> BTUODIS	BSCAN test update register, falling edge of clock to output disabled	—	25	ns
<sup>t</sup> BTUPOEN	BSCAN test update register, falling edge of clock to output enabled	_	25	ns

Note: Rev. A 0.19



### Figure 3.28. JTAG Port Timing Waveforms



## 3.21. Switching Test Conditions

Figure 3.29. shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3.16.

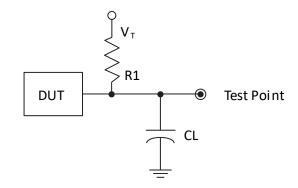


Figure 3.29. Output Test Load, LVTTL and LVCMOS Standards

Table 3.16. Test Fixture Required Components,	<b>Non-Terminated Interfaces</b>
---	----------------------------------

Test Condition	R <sub>1</sub>	CL	Timing Ref.	V <sub>T</sub>
LVTTL and LVCMOS settings (L -> H, H -> L)	8 S	0pF	LVTTL, LVCMOS 3.3 = 1.5V	—
			LVCMOS 2.5 = $V_{CCIO}/2$	—
			LVCMOS 1.8 = $V_{CCIO}/2$	—
			LVCMOS 1.5 = $V_{CCIO}/2$	—
			LVCMOS 1.2 = $V_{CCIO}/2$	—
LVTTL and LVCMOS 3.3 (Z -> H)	188	0pF	1.5	V <sub>OL</sub>
LVTTL and LVCMOS 3.3 (Z -> L)				V <sub>OH</sub>
Other LVCMOS (Z -> H)			V <sub>CCIO</sub> /2	V <sub>OL</sub>
Other LVCMOS (Z -> L)			V <sub>CCIO</sub> /2	V <sub>OH</sub>
LVTTL + LVCMOS (H -> Z)	1		V <sub>OH</sub> - 0.15	V <sub>OL</sub>
LVTTL + LVCMOS (L -> Z)			V <sub>OL</sub> - 0.15	V <sub>OH</sub>

Note: Output test conditions for all other interfaces are determined by the respective standards.

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# 4. Pinout Information

### 4.1. Signal Descriptions

#### Table 4.1. Signal Descriptions

Signal Name	I/O	Descriptions
General Purpose		
P[Edge] [Row/Column Number]_[A/B/C/D/E/F]	1/0	<ul> <li>[Edge] indicates the edge of the device on which the pad is located. Valid edge designations are L (Left), B (Bottom), R (Right), T (Top).</li> <li>[Row/Column Number] indicates the PFU row or the column of the device on which the PIO Group exists. When Edge is T (Top) or (Bottom), only need to specify Row Number. When Edge is L (Left) or R (Right), only need to specify Column Number.</li> <li>[A/B/C/D/E/F] indicates the PIO within the group to which the pad is connected.</li> <li>Some of these user programmable pins are shared with special function pins. When not used as special function pins, these pins can be programmed as I/Os for user logic.</li> <li>During configuration of the user-programmable I/Os, the user has an option to tri-state the I/Os and enable an internal pull-up resistor. This option also applies to unused pins (or those not bonded to a package pin). The default during configuration is for user-programmable I/Os to be tri-stated with an internal pull-up resistor enabled.</li> </ul>
GSRN	I	Global RESET signal (active low). Dedicated pad, when not in use it can be used as an I/O pin.
TSALL	I	TSALL is a dedicated pad for the global output enable signal. When TSALL is high all the outputs are tristated. It is a dual function pin. When not in use, it can be used as an I/O pin.
NC	-	No connect.
GND	-	GND - Ground. Dedicated pins.
V <sub>CC</sub>	-	VCC - The power supply pins for core logic. Dedicated pins.
V <sub>CCAUX</sub>	-	VCCAUX - the Auxiliary power supply pin. This pin powers up a variety of internal circuits including all the differential and referenced input buffers. Dedicated pins.
V <sub>CCIOx</sub>	-	V <sub>CCIO</sub> - The power supply pins for I/O Bank x. Dedicated pins.
SLEEPN <sup>1</sup>	I	Sleep Mode pin - Active low sleep pin. When this pin is held high, the device operates nor- mally. This pin has a weak internal pull-up, but when unused, an external pull-up to V <sub>CC</sub> is recommended. When driven low, the device moves into Sleep mode after a specified time.
PLL and Clock Functions (Us	ed as u	ser programmable I/O pins when not used for PLL or clock pins)
[LOC][0]_PLL[T, C]_IN	_	Reference clock (PLL) input Pads: [LOC] indicates location. Valid designations are ULM (Upper PLL) and LLM (Lower PLL). T = true and C = complement.
[LOC][0]_PLL[T, C]_FB	_	Optional feedback (PLL) input Pads: [LOC] indicates location. Valid designations are ULM (Upper PLL) and LLM (Lower PLL). T = true and C = complement.
PCLK [n]_[1:0]	_	Primary Clock Pads, n per side.
		Test and Programming (Dedicated pins)
TMS	Ι	Test Mode Select input pin, used to control the 1149.1 state machine.
ТСК	Ι	Test Clock input pin, used to clock the 1149.1 state machine.
TDI	Ι	Test Data input pin, used to load data into the device using an 1149.1 state machine.
TDO	0	Output pin -Test Data output pin used to shift data out of the device using 1149.1.

Note: Applies to LA-MachXO "C" devices only. NC for "E" devices.

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### 4.2. Pin Information Summary

Pin Type		LAMXO256C/E		LAMXO640C/E	
		100 TQFP	100 TQFP	144 TQFP	256 ftBGA
Single Ended User I/O		78	74	113	159
Differential Pair User I/O <sup>1</sup>		38	17	43	79
Muxed		6	6	6	6
ТАР	4	4	4	4	
Dedicated (Total Without Supplies)	5	5	5	5	
VCC		2	2	4	4
VCCAUX		1	1	2	2
VCCIO	Bank0	3	2	2	4
	Bank1	3	2	2	4
	Bank2	—	2	2	4
	Bank3	_	2	2	4
GND		8	10	12	18
NC		0	0	0	52
Single Ended/Differential I/O per	Bank0	41/20	18/5	29/10	42/21
Bank	Bank1	37/18	21/4	30/11	40/20
	Bank2	_	14/2	24/9	36/18
	Bank3	—	21/6	30/13	40/20

Note: These devices support emulated LVDS outputs. LVDS inputs are not supported.

Pin Type			LAMXO1200E			LAMXC	02280E	
		100 TQFP	144 TQFP	256 ftBGA	100 TQFP	144 TQFP	256 ftBGA	324 ftBGA
Single Ended User I/O		73	113	211	73	113	211	271
Differential Pair User I/O <sup>1</sup>		27	48	105	30	47	105	134
Muxed		6	6	6	6	6	6	6
ТАР		4	4	4	4	4	4	4
Dedicated (Total Without Supplies)		5	5	5	5	5	5	5
VCC		4	4	4	2	4	4	6
VCCAUX		2	2	2	2	2	2	2
VCCIO	Bank0	1	1	2	1	1	2	2
	Bank1	1	1	2	1	1	2	2
	Bank2	1	1	2	1	1	2	2
	Bank3	1	1	2	1	1	2	2
	Bank4	1	1	2	1	1	2	2
	Bank5	1	1	2	1	1	2	2
	Bank6	1	1	2	1	1	2	2
	Bank7	1	1	2	1	1	2	2
GND		8	12	18	8	12	18	24
NC		0	0	0	0	0	0	0
Single Ended/Differential	Bank0	10/3	14/6	26/13	9/3	13/6	24/12	34/17
I/O per Bank	Bank1	8/2	15/7	28/14	9/3	16/7	30/15	36/18
	Bank2	10/4	15/7	26/13	10/4	15/7	26/13	34/17
	Bank3	11/5	15/7	28/14	11/5	15/7	28/14	34/17
	Bank4	8/3	14/5	27/13	8/3	14/4	29/14	35/17
	Bank5	5/2	10/4	22/11	5/2	10/4	20/10	30/15
	Bank6	10/3	15/6	28/14	10/4	15/6	28/14	34/17
	Bank7	11/5	15/6	26/13	11/5	15/6	26/13	34/17

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Note: These devices support on-chip LVDS buffers for left and right I/O Banks.

### 4.3. Power Supply and NC

Signal	100 TQFP <sup>1</sup>	144 TQFP <sup>1</sup>
VCC	LAMXO256/640: 35, 90	21, 52, 93, 129
	LAMXO1200/2280: 17, 35, 66, 91	
VCCIO0	LAMXO256: 60, 74, 92	LAMXO640: 117, 135
	LAMXO640: 80, 92	LAMXO1200/2280: 135
	LAMXO1200/2280: 94	
VCCI01	LAMXO256: 10, 24, 41	LAMXO640: 82, 98
	LAMXO640: 60, 74	LAMXO1200/2280: 117
	LAMXO1200/2280: 80	
VCCIO2	LAMXO256: None	LAMXO640: 38, 63
	LAMXO640: 29, 41	LAMXO1200/2280: 98
	LAMXO1200/2280: 70	
VCCIO3	LAMXO256: None	LAMXO640: 10, 26
	LAMXO640: 10, 24	LAMXO1200/2280: 82
	LAMXO1200/2280: 56	
VCCIO4	LAMXO256/640: None	LAMXO640: None
	LAMXO1200/2280: 44	LAMXO1200/2280: 63
VCCIO5	LAMXO256/640: None	LAMXO640: None
	LAMXO1200/2280: 27	LAMXO1200/2280: 38
VCCIO6	LAMXO256/640: None	LAMXO640: None
	LAMXO1200/2280: 20	LAMXO1200/2280: 26
VCCIO7	LAMXO256/640: None	LAMXO640: None
	LAMXO1200/2280: 6	LAMXO1200/2280: 10
VCCAUX	LAMXO256/640: 88	53, 128
	LAMXO1200/2280: 36, 90	
GND <sup>2</sup>	LAMXO256: 40, 84, 62, 75, 93, 12, 25, 42	16, 59, 88, 123, 118, 136, 83, 99, 37, 64, 11, 27
	LAMXO640: 40, 84, 81, 93, 62, 75, 30, 42, 12, 25	
	LAMXO1200/2280: 9, 41, 59, 83, 100, 76, 50, 26	
NC <sup>3</sup>		

Notes:

1. Pin orientation follows the conventional order from pin 1 marking of the top side view and counter-clockwise.

2. All grounds must be electrically connected at the board level. For fpBGA and ftBGA packages, the total number of GND balls is less than the actual number of GND logic connections from the die to the common package GND plane.

3. NC pins should not be connected to any active signals, VCC or GND.

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### 4.4. Power Supply and NC (Cont.)

Signal	256 ftBGA <sup>1</sup>	324 ftBGA <sup>1</sup>
VCC	G7, G10, K7, K10	F14, G11, G9, H7, L7, M9
VCCIO0	LAMXO640: F8, F7, F9, F10	G8, G7
	LAMXO1200/2280: F8, F7	
VCCIO1	LAMXO640: H11, G11, K11, J11	G12, G10
	LAMXO1200/2280: F9, F10	
VCCIO2	LAMXO640: L9, L10, L8, L7	J12, H12
	LAMXO1200/2280: H11, G11	
VCCIO3	LAMXO640: K6, J6, H6, G6	L12, K12
	LAMXO1200/2280: K11, J11	
VCCIO4	LAMXO640: None	M12, M11
	LAMXO1200/2280: L9, L10	
VCCIO5	LAMXO640: None	M8, R9
	LAMXO1200/2280: L8, L7	
VCCIO6	LAMXO640: None	M7, K7
	LAMXO1200/2280: K6, J6	
VCCI07	LAMXO640: None	H6, J7
	LAMXO1200/2280: H6, G6	
VCCAUX	Т9, А8	M10, F9
GND <sup>2</sup>	A1, A16, F11, G8, G9, H7, H8, H9, H10, J7, J8, J9, J10,	E14, F16, H10, H11, H8, H9, J10, J11, J4, J8, J9, K10,
	K8, K9, L6, T1, T16	K11, K17, K8, K9, L10, L11, L8, L9, N2, P14, P5, R7
NC <sup>3</sup>	LAMXO640: E4, E5, F5, F6, C3, C2, G4, G5, H4, H5, K5,	-
	K4, M5, M4, P2, P3, N5, N6, M7, M8, N10, N11, R15,	
	R16, P15, P16, M11, L11, N12, N13, M13, M12, K12,	
	J12, F12, F13, E12, E13, D13, D14, B15, A15, C14,	
	B14, E11, E10, E7, E6, D4, D3, B3, B2 <b>LAMXO1200</b> :	
	B14, E11, E10, E7, E6, D4, D3, B3, B2 LAWXO1200: None LAMXO2280: None	

Notes:

1. Pin orientation A1 starts from the upper left corner of the top side view with alphabetical order ascending vertically and numerical order ascending horizontally.

2. All grounds must be electrically connected at the board level. For fpBGA and ftBGA packages, the total number of GND balls is less than the actual number of GND logic connections from the die to the common package GND plane.

3. NC pins should not be connected to any active signals, VCC or GND.

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### 4.5. LA-MachXO256 and LA-MachXO640 Logic Signal Connections: 100 TQFP

Pin Number		LAM	KO256		LAMXO640					
	Ball Function	Bank	Dual Function	Differential	Ball Function	Bank	<b>Dual Function</b>	Differential		
1	PL2A	1		Т	PL2A	3		Т		
2	PL2B	1		С	PL2C	3		Т		
3	PL3A	1		Т	PL2B	3		С		
4	PL3B	1		С	PL2D	3		С		
5	PL3C	1		Т	PL3A	3		Т		
6	PL3D	1		С	PL3B	3		С		
7	PL4A	1		Т	PL3C	3		Т		
8	PL4B	1		С	PL3D	3		С		
9	PL5A	1		Т	PL4A	3				
	10 VCCIO1 1				VCCIO3	3				
11	PL5B	1		С	PL4C	3		Т		
12	GNDIO1	1		-	GNDIO3	3				
13	PL5C	1		Т	PL4D	3		С		
14	PL5D	1	GSRN	С	PL5B	3	GSRN			
15	PL6A	1		T	PL7B	3				
16	PL6B	1	TSALL	C	PL8C	3	TSALL	Т		
17	PL7A	1	10/122	T	PL8D	3	10/122	C		
18	PL7B	1		C	PL9A	3		C		
19	PL7C	1		<u>т</u>	PL9C	3				
20	PL7D	1		C	PL10A	3				
20	PL8A	1		T	PL10C	3				
21	PL8B	1		C	PL11A	3				
22	PL9A	1		т	PL11A PL11C	3				
23	VCCIO1	1		1	VCCIO3	3				
25	GNDIO1	1			GNDIO3	3				
26	TMS	1	TMS		TMS	2	TMS			
20	PL9B	1	11415	С	PB2C	2	11415			
28	ТСК	1	ТСК	C	TCK	2	ТСК			
29	PB2A	1	TCK	т	VCCIO2	2	TCK			
30	PB2R PB2B	1		C	GNDIO2	2				
30	TDO	1	TDO	C	TDO	2	TDO			
32	PB2C	1	100	т	PB4C	2	100			
33	TDI	1	TDI	-	TDI	2	TDI			
33	PB2D	1		С	PB4E	2				
35	VCC	-		C	VCC	-				
36	PB3A	1	PCLK1_1**	Т	PB5B	2	PCLK2_1**			
37	PB3B	1	FCERI_I	C	PB5D	2	FCLKZ_1			
38	PB3D PB3C	1	PCLK1_0**	Т	PB6B	2	PCLK2_0**			
39	PB3C PB3D	1	FULKI_U	C	PB6C	2	FCLKZ_U			
40	GND	-		L	GND	-	+			
40	VCCIO1	1			VCCIO2	2	+			
41 VCCIO1 42 GNDIO1		1			GNDIO2	2	+			
	43 PB4A 1			т	PB8B	2	+			
	43 PB4A 1 44 PB4B 1			C	1 1	2		т		
					PB8C			T C		
45	PB4C			Т	PB8D	2		L		
46	PB4D	1		С	PB9A	2				



Pin Number		LAM	XO256		LAMXO640					
	<b>Ball Function</b>	Bank	<b>Dual Function</b>	Differential	<b>Ball Function</b>	Bank	<b>Dual Function</b>	Differential		
47	PB5A	1			PB9C	2		Т		
48*	SLEEPN	-	SLEEPN		SLEEPN	-	SLEEPN			
49	PB5C	1		Т	PB9D	2		С		
50	PB5D	1		С	PB9F	2				
51	PR9B	0		С	PR11D	1		С		
52	PR9A	0		Т	PR11B	1		С		
53	PR8B	0		С	PR11C	1		Т		
54	PR8A	0		Т	PR11A	1		Т		
55	PR7D	0		С	PR10D	1		С		
56	PR7C 0			Т	PR10C	1		Т		
57	PR7B 0			С	PR10B	1		С		
58	PR7A O			Т	PR10A	1		Т		
59	PR6B	0		С	PR9D	1				
60	VCCIO0	0			VCCI01	1				
61	PR6A	0		Т	PR9B	1				
62	GNDIO0	0			GNDIO1	1				
63	PR5D	0		С	PR7B	1				
64	PR5C	0		Т	PR6C	1				
65	PR5B	0		С	PR6B	1				
66	PR5A	0		Т	PR5D	1				
67	PR4B	0		С	PR5B	1				
68	PR4A	0		Т	PR4D	1				
69	PR3D	0		С	PR4B	1				
70	PR3C	0		Т	PR3D	1				
71	PR3B	0		С	PR3B	1				
72	PR3A	0		Т	PR2D	1				
73	PR2B	0		С	PR2B	1				
74	VCCIOO	0			VCCIO1	1				
75	GNDIO0	0			GNDIO1	1				
76	PR2A	0		Т	PT9F	0		С		
77	PT5C	0			PT9E	0		Т		
78	PT5B	0		С	PT9C	0				
79	PT5A	0		Т	PT9A	0				
80	PT4F	0		С	VCCI00	0				
81	PT4E	0		Т	GNDIO0	0				
82	PT4D	0		C	PT7E	0				
83	PT4C	0	1	T	PT7A	0				
84	GND	-			GND	-				
85	PT4B	0	PCLK0_1**	С	PT6B	0	PCLK0_1**			
86	PT4A	0	PCLK0_0**	T	PT5B	0	PCLK0_0**	С		
87	PT3D	0		C	PT5A	0		T		
88	VCCAUX	-		-	VCCAUX	-				
89	PT3C	0		Т	PT4F	0				
90	VCC	-		-	VCC	-				
91	PT3B	0		С	PT3F	0				
92	VCCIOO	0		,	VCCIO0	0				
93	GNDIO0	0			GNDIOO	0				



Pin Number		LAMX	(0256		LAMXO640				
	<b>Ball Function</b>	Bank	<b>Dual Function</b>	Differential	<b>Ball Function</b>	Bank	<b>Dual Function</b>	Differential	
94	PT3A	0		Т	PT3B	0		С	
95	PT2F	0		С	PT3A	0		Т	
96	PT2E	0		Т	PT2F	0		С	
97	PT2D	0		С	PT2E	0		Т	
98	PT2C	0		Т	PT2B	0		C	
99	PT2B	0		С	PT2C	0			
100	PT2A	0		Т	PT2A	0		Т	

Notes:

NC for "E" devices. 1.

2. Primary clock inputs are single-ended.



## 4.6. LA-MachXO1200 and LA-MachXO2280 Logic Signal Connections: 100 TQFP

Pin			LAMXO1200		LAMXO2280						
Number	<b>Ball Function</b>	Bank	Dual Function	Differential	<b>Ball Function</b>	Bank	Dual Function	Differential			
1	PL2A	7		Т	PL2A	7	LUM0_PLLT_FB_A	Т			
2	PL2B	7		C	PL2B	7	LUM0_PLLC_FB_A	C			
3	PL3C	7		Т	PL3C	7	LUM0_PLLT_IN_A	Т			
4	PL3D	7		С	PL3D	7	LUM0_PLLC_IN_A	С			
5	PL4B	7			PL4B	7					
6	VCCIO7	7			VCCI07	7					
7	PL6A	7		Т*	PL7A	7		Т*			
8	PL6B	7	GSRN	C*	PL7B	7	GSRN	C*			
9	GND	I			GND	-					
10	PL7C	7		Т	PL9C	7		Т			
11	PL7D	7		С	PL9D	7		С			
12	PL8C	7		Т	PL10C	7		Т			
13	PL8D	7		С	PL10D	7		С			
14	PL9C	6			PL11C	6					
15	PL10A	6		T*	PL13A	6		Т*			
16	PL10B 6			C*	PL13B	6		C*			
17	VCC	I			VCC	-					
18	PL11B	6			PL14D	6		С			
19	PL11C	6	TSALL		PL14C	6	TSALL	Т			
20	VCCIO6	6			VCCIO6	6					
21	PL13C	6			PL16C	6					
22	PL14A	6	LLM0_PLLT_FB_A	Т*	PL17A	6	LLM0_PLLT_FB_A	Т*			
23	PL14B	6	LLM0_PLLC_FB_A	C*	PL17B	6	LLM0_PLLC_FB_A	C*			
24	PL15A	6	LLM0_PLLT_IN_A	Т*	PL18A	6	LLM0_PLLT_IN_A	Т*			
25	PL15B	6	LLM0_PLLC_IN_A	C*	PL18B	6	LLM0_PLLC_IN_A	С*			
26**	GNDIO6	-			GNDIO6	-					
	GNDIO5				GNDIO5						
27	VCCIO5	5			VCCIO5	5					
28	TMS	5	TMS		TMS	5	TMS				
29	ТСК	5	ТСК		ТСК	5	ТСК				
30	PB3B	5			PB3B	5					
31	PB4A	5		Т	PB4A	5		Т			
32	PB4B	5		С	PB4B	5		С			
33	TDO	5	TDO		TDO	5	TDO				
34	TDI	5	TDI		TDI	5	TDI				
35	VCC	-			VCC	-					
36	VCCAUX	-			VCCAUX	-					
37	PB6E	5		Т	PB8E	5		Т			
38	PB6F	5		С	PB8F	5		С			
39	PB7B	4	PCLK4_1***		PB10F	4	PCLK4_1***				
40	PB7F	4	PCLK4_0***		PB10B	4	PCLK4_0***				
41	GND	-			GND	-					
42	PB9A	4		Т	PB12A	4		Т			
43	PB9B	4		С	PB12B	4		С			
44	VCCIO4	4			VCCIO4	4					
45	PB10A	4		Т	PB13A	4		Т			

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Pin			LAMXO1200			LAMXO2280					
Number	<b>Ball Function</b>	Bank	Dual Function	Differential	<b>Ball Function</b>	Bank	Dual Function	Differential			
46	PB10B	4		C	PB13B	4		С			
47	NC	-	NC		NC	-	NC				
48	PB11A	4		Т	PB16A	4		Т			
49	PB11B	4		С	PB16B	4		С			
50**	GNDIO3	-			GNDIO3	-					
	GNDIO4				GNDIO4						
51	PR16B	3			PR19B	3					
52	PR15B	3		C*	PR18B	3		C*			
53	PR15A	3		T*	PR18A	3		T*			
54	PR14B	3		C*	PR17B	3		C*			
55	PR14A	3		T*	PR17A	3		T*			
56	VCCIO3	3			VCCIO3	3					
57	PR12B	3		C*	PR15B	3		C*			
58	PR12A	3		Т*	PR15A	3		Т*			
59	GND	-			GND	-					
60	PR10B	3		C*	PR13B	3		C*			
61	PR10A	3		Т*	PR13A	3		T*			
62	PR9B	3		C*	PR11B	3		C*			
63	PR9A	3		Т*	PR11A	3		T*			
64	PR8B	2		C*	PR10B	2		C*			
65	PR8A	2		Т*	PR10A	2		Т*			
66	VCC	-			VCC	-					
67	PR6C	2			PR8C	2					
68	PR6B	2		C*	PR8B	2		C*			
69	PR6A	2		Т*	PR8A	2		Т*			
70	VCCIO2	2			VCCIO2	2					
71	PR4D	2			PR5D	2					
72	PR4B	2		C*	PR5B	2		C*			
73	PR4A	2		T*	PR5A	2		T*			
74	PR2B	2		C	PR3B	2		C*			
75	PR2A	2		Т	PR3A	2		T*			
76**	GNDIO1	-			GNDIO1	-					
	GNDIO2				GNDIO2						
77	PT11C	1			PT15C	1					
78	PT11B	1		С	PT14B	1		С			
79	PT11A	1		Т	PT14A	1		Т			
80	VCCI01	1			VCCI01	1					
81	PT9E	1			PT12D	1		С			
82	PT9A	1			PT12C	1		Т			
83	GND	-			GND	-					
84	PT8B	1		С	PT11B	1		С			
85	PT8A	1		Т	PT11A	1		Т			
86	PT7D	1	PCLK1_1***		PT10B	1	PCLK1_1***				
87	PT6F	0	PCLK1_0***		PT9B	1	PCLK1_0***				
88	PT6D	0		С	PT8F	0		С			
89	PT6C	0		Т	PT8E	0		Т			
90	VCCAUX	-			VCCAUX	-					

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Pin			LAMXO1200				LAMXO2280	LAMXO2280					
Number	<b>Ball Function</b>	Bank	Dual Function	Differential	<b>Ball Function</b>	Bank	<b>Dual Function</b>	Differential					
91	VCC	-			VCC	-							
92	PT5B	0			PT6D	0							
93	PT4B	0			PT6F	0							
94	VCCI00	0			VCCI00	0							
95	PT3D	0		C	PT4B	0		С					
96	PT3C	0		Т	PT4A	0		Т					
97	PT3B	0			PT3B	0							
98	PT2B	0		C	PT2B	0		C					
99	PT2A	0		Т	PT2A	0		Т					
100**	GNDIO0	-			GNDIO0	-							
	GNDIO7				GNDIO7								

Notes:

1. Supports true LVDS outputs.

2. Double bonded to the pin.

3. Primary clock inputs are single-ended.

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#### 4.7. LA-MachXO640, LA-MachXO1200 and LA-MachXO2280 Logic Signal **Connections: 144 TQFP**

Pin			AMX0640	•			LAMXO1200				LAMXO2280	
Number	Ball Function	Bank	1	Differential	Ball Function	Bank	Dual Function	Differential	Ball Function	Bank	Dual Function	Differential
1	PL2A	3		Т	PL2A	7		Т	PL2A	7	LUM0_PLLT_FB_A	Т
2	PL2C	3		Т	PL2B	7		С	PL2B	7	LUM0_PLLC_FB_A	С
3	PL2B	3		С	PL3A	7		T*	PL3A	7		T*
4	PL3A	3		Т	PL3B	7		C*	PL3B	7		C*
5	PL2D	3		С	PL3C	7		Т	PL3C	7	LUM0_PLLT_IN_A	Т
6	PL3B	3		С	PL3D	7		С	PL3D	7	LUM0_PLLC_IN_A	С
7	PL3C	3		Т	PL4A	7		T*	PL4A	7		T*
8	PL3D	3		С	PL4B	7		C*	PL4B	7		C*
9	PL4A	3			PL4C	7			PL4C	7		
10	VCCIO3	3			VCCI07	7			VCCI07	7		
11	GNDIO3	3			GNDIO7	7			GNDIO7	7		
12	PL4D	3			PL5C	7			PL6C	7		
13	PL5A	3		т	PL6A	7		T*	PL7A	7		Т*
13	PL5B	3	GSRN	C	PL6B	7	GSRN	C*	PL7B	7	GSRN	C*
15	PL5D	3	GSIN	c	PL6D	7	GSIN	č	PL7D	7	Gold	č
15	GND	-			GND	-			GND	-		
				т				т				т
17	PL6C	3		Т	PL7C	7		Т	PL9C	7		T
18	PL6D	3		C T	PL7D	7		C *	PL9D	7		C T*
19	PL7A	3		Т	PL10A	6		T*	PL13A	6		T*
20	PL7B	3		С	PL10B	6		C*	PL13B	6		C*
21	VCC	-			VCC	-			VCC	-		
22	PL8A	3		Т	PL11A	6		T*	PL13D	6		
23	PL8B	3		С	PL11B	6		C*	PL14D	6		С
24	PL8C	3	TSALL		PL11C	6	TSALL		PL14C	6	TSALL	Т
25	PL9C	3		Т	PL12B	6			PL15B	6		
26	VCCIO3	3			VCCIO6	6			VCCIO6	6		
27	GNDIO3	3			GNDIO6	6			GNDIO6	6		
28	PL9D	3		С	PL13D	6			PL16D	6		
29	PL10A	3		Т	PL14A	6	LLM0_PLLT_FB_A	T*	PL17A	6	LLM0_PLLT_FB_A	T*
30	PL10B	3		С	PL14B	6	LLM0_PLLC_FB_A	C*	PL17B	6	LLM0_PLLC_FB_A	C*
31	PL10C	3		Т	PL14C	6		Т	PL17C	6		Т
32	PL11A	3		Т	PL14D	6		С	PL17D	6		С
33	PL10D	3		С	PL15A	6	LLM0_PLLT_IN_A	T*	PL18A	6	LLM0_PLLT_IN_A	T*
34	PL11C	3		т	PL15B	6	LLM0_PLLC_IN_A	C*	PL18B	6	 LLM0_PLLC_IN_A	C*
35	PL11B	3		С	PL16A	6		Т	PL19A	6		Т
36	PL11D	3		C	PL16B	6		C	PL19B	6		C
37	GNDIO2	2			GNDIO5	5			GNDIO5	5		
38	VCCIO2	2			VCCIO5	5			VCCIO5	5		
			TNAS				TNAC				TMC	
39	TMS	2	TMS		TMS	5	TMS	-	TMS	5	TMS	
40	PB2C	2		т	PB2C	5 5		T C	PB2A	5 5		T
41	PB3A	2	TCY	Т	PB2D		TC''	L	PB2B		TCY	С
42	TCK	2	TCK		TCK	5	ТСК	-	TCK	5	ТСК	-
43	PB3B	2		C –	PB3A	5		T	PB3A	5		T
44	PB3C	2		T	PB3B	5		C	PB3B	5		C
45	PB3D	2		С	PB4A	5		Т	PB4A	5		Т
46	PB4A	2		Т	PB4B	5		С	PB4B	5		С
47	TDO	2	TDO		TDO	5	TDO		TDO	5	TDO	
48	PB4B	2		С	PB4D	5			PB4D	5		
49	PB4C	2		Т	PB5A	5		Т	PB5A	5		Т
50	PB4D	2		С	PB5B	5		С	PB5B	5		С
51	TDI	2	TDI		TDI	5	TDI		TDI	5	TDI	
52	VCC	-			VCC	-			VCC	-		
53	VCCAUX	-			VCCAUX	-		1	VCCAUX	-		
54	PB5A	2		т	PB6F	5			PB8F	5		
55	PB5B	2	PCLKT2_1***	С	PB7B	4	PCLK4_1***	1	PB10F	4	PCLK4_1***	
56	PB5D	2		-	PB7C	4		т	PB10C	4		Т
	PB6A	2	1	т	PB7D	4		C	PB10D	4		C

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Pin		L	AMXO640				LAMXO1200				LAMXO2280	
Number	Ball Function	Bank	Dual Function	Differential	Ball Function	Bank	Dual Function	Differential	Ball Function	Bank	Dual Function	Differential
58	PB6B	2	PCLKT2_0***	С	PB7F	4	PCLK4_0***		PB10B	4	PCLK4_0***	
59	GND	-			GND	-			GND	-		
60	PB7C	2			PB9A	4		т	PB12A	4		т
61	PB7E	2			PB9B	4		С	PB12B	4		С
62	PB8A	2			PB9E	4			PB12E	4		
63	VCCIO2	2			VCCIO4	4			VCCIO4	4		
64	GNDIO2	2			GNDIO4	4			GNDIO4	4		
65	PB8C	2		Т	PB10A	4		т	PB13A	4		т
66	PB8D	2		C	PB10B	4		C	PB13B	4		C
67	PB9A	2		T	PB10C	4		т	PB13C	4		т
68	PB9C	2		т	PB10D	4		C	PB13D	4		C
69	PB9B	2		C	PB10F	4			PB14D	4		
70**	SLEEPN	-	SLEEPN	C	NC	-			NC	-		
70	PB9D	2	JLLEFN	С	PB11C	4		т	PB16C	4		т
				L				C				-
72	PB9F	2		-	PB11D	4			PB16D	4		С
73	PR11D	1		С	PR16B	3		C	PR20B	3		С
74	PR11B	1		C	PR16A	3		T	PR20A	3		Т
75	PR11C	1		Т	PR15B	3		C*	PR19B	3		C
76	PR10D	1		C	PR15A	3		T*	PR19A	3		Т
77	PR11A	1		Т	PR14D	3		С	PR17D	3		С
78	PR10B	1		С	PR14C	3		Т	PR17C	3		Т
79	PR10C	1		Т	PR14B	3		C*	PR17B	3		C*
80	PR10A	1		Т	PR14A	3		T*	PR17A	3		Т*
81	PR9D	1			PR13D	3			PR16D	3		
82	VCCI01	1			VCCIO3	3			VCCI03	3		
83	GNDIO1	1			GNDIO3	3			GNDIO3	3		
84	PR9A	1			PR12B	3		C*	PR15B	3		C*
85	PR8C	1			PR12A	3		Т*	PR15A	3		Т*
86	PR8A	1			PR11B	3		C*	PR14B	3		C*
87	PR7D	1			PR11A	3		Т*	PR14A	3		Т*
88	GND	-			GND	-			GND	-		
89	PR7B	1		С	PR10B	3		C*	PR13B	3		C*
90	PR7A	1		Т	PR10A	3		T*	PR13A	3		T*
91	PR6D	1		С	PR8B	2		C*	PR10B	2		C*
92	PR6C	1		Т	PR8A	2		T*	PR10A	2		T*
93	VCC	-			VCC	-			VCC	-		
94	PR5D	1			PR6B	2		C*	PR8B	2		C*
95	PR5B	1			PR6A	2		T*	PR8A	2		T*
96	PR4D	1			PR5B	2		C*	PR7B	2		C*
97	PR4B	1		С	PR5A	2		T*	PR7A	2		т*
98	VCCI01	1		C	VCCIO2	2			VCCIO2	2		
99	GNDIO1	1			GNDIO2	2			GNDIO2	2		
100	PR4A	1		т	PR4C	2			PR5C	2		
100	PR4A PR3D	1		C	PR4C PR4B	2		C*	PR5C PR5B	2		C*
				Т								-
102	PR3C	1			PR4A	2		T*	PR5A	2		T*
103	PR3B	1		С	PR3D	2		C	PR4D	2		C
104	PR2D	1		C	PR3C	2		T	PR4C	2		T
105	PR3A	1		Т	PR3B	2		C*	PR4B	2		C*
106	PR2B	1		C	PR3A	2		T*	PR4A	2		T*
107	PR2C	1		Т	PR2B	2		С	PR3B	2		C*
108	PR2A	1		Т	PR2A	2		Т	PR3A	2		T*
109	PT9F	0		С	PT11D	1		С	PT16D	1		С
110	PT9D	0		С	PT11C	1		Т	PT16C	1		Т
111	PT9E	0		Т	PT11B	1		С	PT16B	1		С
112	PT9B	0		С	PT11A	1		Т	PT16A	1		Т
113	PT9C	0		Т	PT10F	1		С	PT15D	1	<u> </u>	С
114	PT9A	0		Т	PT10E	1		Т	PT15C	1		Т
115	PT8C	0			PT10D	1		С	PT14B	1		С
116	PT8B	0		С	PT10C	1		Т	PT14A	1		Т
117	VCCI00	0			VCCI01	1			VCCI01	1		
118	GNDI00	0			GNDIO1	1			GNDIO1	1		1



Pin		L	AMXO640				LAMXO1200				LAMXO2280	
Number	Ball Function	Bank	Dual Function	Differential	Ball Function	Bank	Dual Function	Differential	Ball Function	Bank	Dual Function	Differential
119	PT8A	0		Т	PT9F	1		С	PT12F	1		С
120	PT7E	0			PT9E	1		Т	PT12E	1		Т
121	PT7C	0			PT9B	1		С	PT12D	1		С
122	PT7A	0			PT9A	1		Т	PT12C	1		Т
123	GND	-			GND	-			GND	-		
124	PT6B	0	PCLK0_1***	С	PT7D	1	PCLK1_1***		PT10B	1	PCLK1_1***	
125	PT6A	0		Т	PT7B	1		С	PT9D	1		С
126	PT5C	0			PT7A	1		Т	PT9C	1		Т
127	PT5B	0	PCLK0_0***		PT6F	0	PCLK1_0***		PT9B	1	PCLK1_0***	
128	VCCAUX	-			VCCAUX	-			VCCAUX	-		
129	VCC	-			VCC	-			VCC	-		
130	PT4D	0			PT5D	0		С	PT7B	0		С
131	PT4B	0		С	PT5C	0		Т	PT7A	0		т
132	PT4A	0		Т	PT5B	0		С	PT6D	0		
133	PT3F	0			PT5A	0		Т	PT6E	0		Т
134	PT3D	0			PT4B	0			PT6F	0		С
135	VCCI00	0			VCCI00	0			VCCI00	0		
136	GNDI00	0			GNDI00	0			GNDIO0	0		
137	PT3B	0		С	PT3D	0		С	PT4B	0		т
138	PT2F	0		С	PT3C	0		Т	PT4A	0		С
139	PT3A	0		Т	PT3B	0		С	PT3B	0		С
140	PT2D	0		С	PT3A	0		Т	PT3A	0		Т
141	PT2E	0		Т	PT2D	0		С	PT2D	0		С
142	PT2B	0		С	PT2C	0		Т	PT2C	0		Т
143	PT2C	0		Т	PT2B	0		С	PT2B	0		С
144	PT2A	0		Т	PT2A	0		Т	PT2A	0		Т

Notes:

1. Supports true LVDS outputs.

NC for "E" devices. 2.

3. Primary clock inputs arer single-ended.



## 4.8. LA-MachXO640, LA-MachXO1200 and LA-MachXO2280 Logic Signal Connections: 256 ftBGA

		LAM	KO640				LAN	1XO1200				LAN	/XO2280	
Ball	Ball		Dual Function	Differential	Ball	Ball	Bank	Dual Function	Differential	Ball	Ball	Bank	Dual Function	Differential
Number	Function				Number	Function				Number	Function			
GND	GNDIO3	3			GND	GNDIO7	7			GND	GNDIO7	7		
VCCIO3	VCCIO3	3			VCCI07	VCCI07	7			VCCI07	VCCI07	7		
E4	NC				E4	PL2A	7		Т	E4	PL2A	7	LUMO PLLT FB A	Т
E5	NC				E5	PL2B	7		С	E5	PL2B	7	LUMO PLLC FB A	С
F5	NC				F5	PL3A	7		T**	F5	PL3A	7		T**
F6	NC				F6	PL3B	7		C**	F6	PL3B	7		C**
F3	PL3A	3		Т	F3	PL3C	7		T	F3	PL3C	7	LUM0_PLLT_IN_A	Т
F4	PL3B	3		C	F4	PL3D	7		C	F4	PL3D	7	LUM0_PLLC_IN_A	C
E3	PL2C	3		т	E3	PL4A	7		T**	E3	PL4A	7	LONIO_I LLC_IN_/	T**
E2	PL2D	3		C	E2	PL4B	7		C**	E2	PL4B	7		C**
C3	NC	5			C3	PL4C	7		Т	C3	PL4C	7		т
C2	NC				C2	PL4C PL4D	7		c	C2	PL4C PL4D	7		C
B1	PL2A	3		Т	B1	PL4D PL5A	7		T**	B1	PL4D PL5A	7		T**
							7		C**			7		C**
C1	PL2B	3		С	C1	PL5B			ر	C1	PL5B			<u>ر</u>
VCCIO3	VCCIO3	3			VCCI07	VCCI07	7			VCCI07	VCCI07	7		
GND	GNDIO3	3			GND	GNDI07	7			GND	GNDIO7	7		
D2	PL3C	3		Т	D2	PL5C	7		Т	D2	PL6C	7		Т
D1	PL3D	3		С	D1	PL5D	7		С	D1	PL6D	7		C
F2	PL5A	3		Т	F2	PL6A	7		T**	F2	PL7A	7		T**
G2	PL5B	3	GSRN	С	G2	PL6B	7	GSRN	C**	G2	PL7B	7	GSRN	C**
E1	PL4A	3		Т	E1	PL6C	7		Т	E1	PL7C	7		Т
F1	PL4B	3		С	F1	PL6D	7		С	F1	PL7D	7		С
G4	NC				G4	PL7A	7		T**	G4	PL8A	7		T**
G5	NC				G5	PL7B	7		C**	G5	PL8B	7		C**
GND	GND	-			GND	GND	-			GND	GND	-		
G3	PL4C	3		Т	G3	PL7C	7		Т	G3	PL8C	7		Т
H3	PL4D	3		С	H3	PL7D	7		С	H3	PL8D	7		С
H4	NC				H4	PL8A	7		T**	H4	PL9A	7		T**
H5	NC				H5	PL8B	7		C**	H5	PL9B	7		C**
-	-				VCCI07	VCCI07	7			VCCI07	VCCI07	7		
-	-				GND	GNDI07	7			GND	GNDIO7	7		
G1	PL5C	3		т	G1	PL8C	7		т	G1	PL10C	7		Т
H1	PL5D	3		С	H1	PL8D	7		С	H1	PL10D	7		С
H2	PL6A	3		Т	H2	PL9A	6		T**	H2	PL11A	6		T**
J2	PL6B	3		C	J2	PL9B	6		C**	J2	PL11B	6		C**
J3	PL7C	3		T	J3	PL9C	6		T	J3	PL11C	6		T
КЗ	PL7D	3		C	K3	PL9D	6		C C	КЗ	PL11D	6		C
J1	PL6C	3		т	J1	PL10A	6		T**	J1	PL12A	6		T**
-	-	3			VCCIO6	VCCIO6	6		'	VCCIO6	VCCIO6	6		1
-							6							
- K1		3		С	GND K1	GNDIO6	ь 6		C**	GND K1	GNDIO6	6 6		C**
	PL6D					PL10B					PL12B			
K2	PL9A	3		Т	K2	PL10C	6		Т	K2	PL12C	6		Т
L2	PL9B	3		C	L2	PL10D	6		C	L2	PL12D	6		C
L1	PL7A	3		T	L1	PL11A	6		T**	L1	PL13A	6		T**
M1	PL7B	3		С	M1	PL11B	6		C**	M1	PL13B	6		C**
P1	PL8D	3		С	P1	PL11D	6		C	P1	PL14D	6		С
N1	PL8C	3	TSALL	Т	N1	PL11C	6	TSALL	Т	N1	PL14C	6	TSALL	Т
L3	PL10A	3		Т	L3	PL12A	6		T**	L3	PL15A	6		T**
M3	PL10B	3		С	M3	PL12B	6		C**	M3	PL15B	6		C**
M2	PL9C	3		Т	M2	PL12C	6		Т	M2	PL15C	6		Т
N2	PL9D	3		С	N2	PL12D	6		С	N2	PL15D	6		С
VCCIO3	VCCIO3	3			VCCIO6	VCCIO6	6			VCCIO6	VCCIO6	6		
GND	GNDIO3	3			GND	GNDIO6	6			GND	GNDIO6	6		
J4	PL8A	3		Т	J4	PL13A	6		T**	J4	PL16A	6		T**
J5	PL8B	3		С	J5	PL13B	6		C**	J5	PL16B	6		C**
R1	PL11A	3		Т	R1	PL13C	6		Т	R1	PL16C	6		Т
R2	PL11B	3		С	R2	PL13D	6		С	R2	PL16D	6		С

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		LAM	KO640				LAN	1XO1200				LAN	1XO2280	
Ball	Ball	Bank	<b>Dual Function</b>	Differential	Ball	Ball	Bank	Dual Function	Differential	Ball	Ball	Bank	Dual Function	Differential
Number	Function				Number	Function				Number	Function			
-	-	-			-	-	-			GND	GND	-		
K5	NC				K5	PL14A	6	LLM0_PLLT_FB_A	T**	K5	PL17A	6	LLM0_PLLT_FB_A	T**
K4	NC	-			K4	PL14B	6	LLM0_PLLC_FB_A	C**	K4	PL17B	6	LLM0_PLLC_FB_A	C**
L5	PL10C	3		Т	L5	PL14C	6		Т	L5	PL17C	6		Т
L4	PL10D	3		С	L4	PL14D	6		C	L4	PL17D	6		C
M5	NC				M5	PL15A	6	LLM0_PLLT_IN_A	T**	M5	PL18A	6	LLM0_PLLT_IN_A	T**
M4	NC				M4	PL15B	6	LLM0_PLLC_IN_A	C**	M4	PL18B	6	LLM0_PLLC_IN_A	C**
N4	PL11C	3		T	N4	PL16A	6		T	N4	PL19A	6		Т
N3	PL11D	3		С	N3	PL16B	6		С	N3	PL19B	6		С
VCCIO3	VCCIO3	3			VCCIO6	VCCIO6	6			VCCIO6	VCCIO6	6		
GND	GNDIO3	3			GND	GNDIO6	6			GND	GNDIO6	6		
GND	GNDIO2	2			GND	GNDIO5	5 5			GND	GNDIO5	5 5		
VCCIO2 P4	VCCIO2 TMS		TMS		VCCIO5 P4	VCCIO5 TMS		TMS		VCCIO5 P4	VCCIO5 TMS	5	TMS	
P4 P2	NC	2	11VI5		P4 P2	PB2A	5 5	TIVI5	т	P4 P2	PB2A	5	11VI5	т
P3 N5	NC NC				P3 N5	PB2B PB2C	5 5		C T	P3 N5	PB2B PB2C	5 5		C T
R3	TCK	2	ТСК		R3	TCK	5	ТСК	1	R3	TCK	5	ТСК	
N6	NC	2	TCK		N6	PB2D	5	ICN	С	N6	PB2D	5	ICK	с
T2	PB2A	2		Т	T2	PB3A	5		т	T2	PB3A	5		т
T3	PB2A PB2B	2		C	T3	PB3B	5		C	T3	PB3B	5		C I
R4	PB2D PB2C	2		T	R4	PB3D PB3C	5		т	R4	PB3D PB3C	5		Т
R5	PB2D	2		C	R5	PB3D	5		C	R5	PB3D	5		C C
P5	PB3A	2		T	P5	PB4A	5		T	P5	PB4A	5		T
P6	PB3B	2		C	P6	PB4B	5		C	P6	PB4B	5		C
T5	PB3C	2		T	T5	PB4C	5		Т	T5	PB4C	5		Т
M6	TDO	2	TDO		M6	TDO	5	TDO		M6	TDO	5	TDO	
T4	PB3D	2		С	T4	PB4D	5		С	T4	PB4D	5		С
R6	PB4A	2		Т	R6	PB5A	5		т	R6	PB5A	5		т
GND	GNDIO2	2			GND	GNDIO5	5			GND	GNDIO5	5		
VCCIO2	VCCIO2	2			VCCI05	VCCIO5	5			VCCI05	VCCIO5	5		
Т6	PB4B	2		С	Т6	PB5B	5		С	Т6	PB5B	5		С
N7	TDI	2	TDI		N7	TDI	5	TDI		N7	TDI	5	TDI	
Т8	PB4C	2		Т	Т8	PB5C	5		Т	Т8	PB6A	5		Т
T7	PB4D	2		С	T7	PB5D	5		C	T7	PB6B	5		С
M7	NC				M7	PB6A	5		Т	M7	PB7C	5		Т
M8	NC				M8	PB6B	5		С	M8	PB7D	5		С
Т9	VCCAUX	-			Т9	VCCAUX	-			Т9	VCCAUX	-		
R7	PB4E	2		Т	R7	PB6C	5		Т	R7	PB8C	5		Т
R8	PB4F	2		С	R8	PB6D	5		C	R8	PB8D	5		С
-	-				VCCIO5	VCCI05	5			VCCIO5	VCCI05	5		
-	-				GND	GNDIO5	5			GND	GNDIO5	5		
P7	PB5C	2		Т	P7	PB6E	5		Т	P7	PB9A	4		Т
P8	PB5D	2		С	P8	PB6F	5		С	P8	PB9B	4		С
N8	PB5A	2		Т	N8	PB7A	4		Т	N8	PB10E	4		Т
N9	PB5B	2	PCLK2_1****	С	N9	PB7B	4	PCLK4_1****	C	N9	PB10F	4	PCLK4_1****	С
P10	PB7B	2		С	P10	PB7D	4		C	P10	PB10D	4		С
P9	PB7A	2		Т	P9	PB7C	4		Т	P9	PB10C	4		Т
M9	PB6B	2	PCLK2_0****	С	M9	PB7F	4	PCLK4_0****	С	M9	PB10B	4	PCLK4_0****	С
-	-				VCCIO4	VCCIO4	4			VCCIO4	VCCIO4	4		
-	-				GND	GNDIO4	4			GND	GNDIO4	4		
M10	PB6A	2		Т	M10	PB7E	4		Т	M10	PB10A	4		Т
R9	PB6C	2		Т	R9	PB8A	4		Т	R9	PB11C	4		Т
R10	PB6D	2		С	R10	PB8B	4		C	R10	PB11D	4		C
T10	PB7C	2		Т	T10	PB8C	4		Т	T10	PB12A	4		Т
T11	PB7D	2		С	T11	PB8D	4		С	T11	PB12B	4		С
N10	NC				N10	PB8E	4		T	N10	PB12C	4		Т
N11	NC	_			N11	PB8F	4		С	N11	PB12D	4		C
VCCIO2	VCCIO2	2			VCCIO4	VCCIO4	4			VCCIO4	VCCIO4	4		
GND	GNDIO2	2			GND	GNDIO4	4			GND	GNDIO4	4		
R11	PB7E	2		Т	R11	PB9A	4		Т	R11	PB13A	4		Т



		LAM)	KO640				LAN	1XO1200				LAN	1XO2280	
Ball	Ball		Dual Function	Differential	Ball	Ball	Bank	Dual Function	Differential	Ball	Ball	Bank	Dual Function	Differential
Number	Function				Number	Function				Number	Function			
R12	PB7F	2		С	R12	PB9B	4		С	R12	PB13B	4		С
P11	PB8A	2		т	P11	PB9C	4		Т	P11	PB13C	4		Т
P12	PB8B	2		С	P12	PB9D	4		С	P12	PB13D	4		С
T13	PB8C	2		Т	T13	PB9E	4		Т	T13	PB14A	4		Т
T12	PB8D	2		С	T12	PB9F	4		С	T12	PB14B	4		С
R13	PB9A	2		Т	R13	PB10A	4		Т	R13	PB14C	4		Т
R14	PB9B	2		С	R14	PB10B	4		C	R14	PB14D	4		С
GND	GND	-			GND	GND	-			GND	GND	-		
T14	PB9C	2		Т	T14	PB10C	4		Т	T14	PB15A	4		Т
T15	PB9D	2		С	T15	PB10D	4		С	T15	PB15B	4		С
P13***	SLEEPN	-	SLEEPN		P13	NC	-			P13	NC	-		
P14	PB9F	2			P14	PB10F	4			P14	PB15D	4		
R15	NC				R15	PB11A	4		Т	R15	PB16A	4		Т
R16	NC				R16	PB11B	4		С	R16	PB16B	4		С
P15	NC				P15	PB11C	4		т	P15	PB16C	4		т
P16	NC				P16	PB11D	4		С	P16	PB16D	4		С
VCCIO2	VCCIO2	2			VCCIO4	VCCIO4	4			VCCIO4	VCCIO4	4		1
GND	GNDIO2	2			GND	GNDIO4	4			GND	GNDIO4	4		
GND	GNDIO1	1			GND	GNDIO3	3			GND	GNDIO3	3		
VCCI01	VCCI01	1			VCCI03	VCCIO3	3			VCCIO3	VCCIO3	3		
M11	NC	-			M11	PR16B	3		С	M11	PR20B	3		С
L11	NC				L11	PR16A	3		T	L11	PR20A	3		T
N12	NC				N12	PR15B	3		C**	N12	PR18B	3		C**
N13	NC				N12	PR15A	3		T**	N12	PR18A	3		T**
M13	NC				M13	PR14D	3		c	M13	PR17D	3		С
M12	NC				M12	PR14C	3		т	M12	PR17C	3		т
N14	PR11D	1		С	N14	PR14C	3		C**	N14	PR17C	3		C**
	PR11D PR11C			т	N14	PR14B PR14A	3		T**	N14	PR17B PR17A	3		T**
N15 L13	PR11C PR11B	1		C	L13	PR14A PR13D	3		C	L13	PR17A PR16D	3		C
L13 L12	PR11B PR11A	1		т	L13 L12	PR13D PR13C	3		т	L13 L12	PR16D PR16C	3		т
				C					C**					C**
M14	PR10B	1		L	M14	PR13B	3		ر	M14	PR16B	3		ر
VCCI01	VCCI01	1			VCCIO3	VCCIO3	3			VCCIO3	VCCIO3	3		
GND	GNDIO1	1		-	GND	GNDIO3	3			GND	GNDIO3	3		
L14	PR10A	1		Т	L14	PR13A	3		T**	L14	PR16A	3		T**
N16	PR10D	1		C	N16	PR12D	3		С	N16	PR15D	3		C
M16	PR10C	1		Т	M16	PR12C	3		T	M16	PR15C	3		T
M15	PR9D	1		С	M15	PR12B	3		C**	M15	PR15B	3		C**
L15	PR9C	1		Т	L15	PR12A	3		T**	L15	PR15A	3		T**
L16	PR9B	1		С	L16	PR11D	3		С	L16	PR14D	3		С
K16	PR9A	1		Т	K16	PR11C	3		Т	K16	PR14C	3		Т
K13	PR8D	1		C	K13	PR11B	3		C**	K13	PR14B	3		C**
J13	PR8C	1		Т	J13	PR11A	3		T**	J13	PR14A	3		T**
GND	GND	-			GND	GND	-			GND	GND	-		-
K14	PR8B	1		С	K14	PR10D	3		С	K14	PR13D	3		С
J14	PR8A	1		Т	J14	PR10C	3		Т	J14	PR13C	3		Т
K15	PR7D	1		С	K15	PR10B	3		C**	K15	PR13B	3		C**
J15	PR7C	1		Т	J15	PR10A	3		T**	J15	PR13A	3		T**
-	-				GND	GNDIO3	3			GND	GNDIO3	3		ļ
-	-				VCCIO3	VCCIO3	3			VCCIO3	VCCIO3	3		
K12	NC				K12	PR9D	3		C	K12	PR11D	3		С
J12	NC				J12	PR9C	3		Т	J12	PR11C	3		Т
J16	PR7B	1		С	J16	PR9B	3		C**	J16	PR11B	3		C**
H16	PR7A	1		Т	H16	PR9A	3		T**	H16	PR11A	3		T**
H15	PR6B	1		С	H15	PR8D	2		С	H15	PR10D	2		С
G15	PR6A	1		Т	G15	PR8C	2		Т	G15	PR10C	2		Т
H14	PR5D	1		С	H14	PR8B	2		C**	H14	PR10B	2		C**
G14	PR5C	1		Т	G14	PR8A	2		T**	G14	PR10A	2		T**
GND	GNDIO1	1			GND	GNDIO2	2			GND	GNDIO2	2		
VCCI01	VCCI01	1			VCCIO2	VCCIO2	2			VCCIO2	VCCIO2	2		
H13	PR6D	1		С	H13	PR7D	2		С	H13	PR9D	2		С
H12	PR6C	1		Т	H12	PR7C	2		Т	H12	PR9C	2		Т



		LAM	KO640				LAN	1XO1200				LAN	1XO2280	
Ball Number	Ball Function	Bank	Dual Function	Differential	Ball Number	Ball Function	Bank	Dual Function	Differential	Ball Number	Ball Function	Bank	Dual Function	Differential
G13	PR4D	1		С	G13	PR7B	2		C**	G13	PR9B	2		C**
G12	PR4C	1		Т	G12	PR7A	2		T**	G12	PR9A	2		T**
G16	PR5B	1		С	G16	PR6D	2		С	G16	PR7D	2		С
F16	PR5A	1		Т	F16	PR6C	2		Т	F16	PR7C	2		Т
F15	PR4B	1		С	F15	PR6B	2		C**	F15	PR7B	2		C**
E15	PR4A	1		Т	E15	PR6A	2		T**	E15	PR7A	2		T**
E16	PR3B	1		С	E16	PR5D	2		С	E16	PR6D	2		С
D16	PR3A	1		Т	D16	PR5C	2		Т	D16	PR6C	2		Т
VCCI01	VCCI01	1			VCCIO2	VCCIO2	2			VCCIO2	VCCIO2	2		
GND	GNDI01	1			GND	GNDIO2	2			GND	GNDIO2	2		
D15	PR2D	1		С	D15	PR5B	2		C**	D15	PR6B	2		C**
C15	PR2C	1		Т	C15	PR5A	2		T**	C15	PR6A	2		T**
C16	PR2B	1		С	C16	PR4D	2		C	C16	PR5D	2		C
B16	PR2A	1		T	B16	PR4C	2		T	B16	PR5C	2		T
F14	PR3D	1		C	F14	PR4B	2		C**	F14	PR5B	2		C**
E14	PR3C	1		Т	E14	PR4A	2		T**	E14	PR5A	2		T**
-	-	-			-	-	-		6	GND	GND	-		6
F12	NC				F12	PR3D	2		C T	F12	PR4D	2		C T
F13	NC				F13	PR3C	2		T C**	F13	PR4C	2		T C**
E12	NC				E12	PR3B	2		T**	E12	PR4B	2		T**
E13 D13	NC NC				E13 D13	PR3A PR2B	2		C	E13 D13	PR4A PR3B	2		C**
D13	NC				D13	PR2B PR2A	2		Т	D13	PR3B PR3A	2		T**
VCCIO0	VCCIOO	0			VCCIO2	VCCIO2	2		1	VCCIO2	VCCIO2	2		1
GND	GNDIO0	0			GND	GNDIO2	2			GND	GNDIO2	2		
GND	GNDIO0	0			GND	GNDI01	1			GND	GNDI01	1		
VCCIOO	VCCIOO	0			VCCI01	VCCI01	1			VCCI01	VCCIO1	1		
B15	NC	0			B15	PT11D	1		С	B15	PT16D	1		С
A15	NC				A15	PT11C	1		т	A15	PT16C	1		т
C14	NC				C14	PT11B	1		C	C14	PT16B	1		C
B14	NC				B14	PT11A	1		T	B14	PT16A	1		T
C13	PT9F	0		С	C13	PT10F	1		С	C13	PT15D	1		С
B13	PT9E	0		T	B13	PT10E	1		Т	B13	PT15C	1		T
E11	NC				E11	PT10D	1		С	E11	PT15B	1		С
E10	NC				E10	PT10C	1		Т	E10	PT15A	1		Т
D12	PT9D	0		С	D12	PT10B	1		С	D12	PT14D	1		С
D11	PT9C	0		Т	D11	PT10A	1		Т	D11	PT14C	1		Т
A14	PT7F	0		С	A14	PT9F	1		С	A14	PT14B	1		С
A13	PT7E	0		Т	A13	PT9E	1		Т	A13	PT14A	1		т
C12	PT8B	0		С	C12	PT9D	1		С	C12	PT13D	1		С
C11	PT8A	0		Т	C11	PT9C	1		Т	C11	PT13C	1		Т
-	-				VCCI01	VCCI01	1			VCCI01	VCCI01	1		
-	-				GND	GNDI01	1			GND	GNDIO1	1		
B12	PT7B	0		С	B12	PT9B	1		С	B12	PT12D	1		С
B11	PT7A	0		Т	B11	PT9A	1		Т	B11	PT12C	1		Т
A12	PT7D	0		С	A12	PT8F	1		С	A12	PT12B	1		С
A11	PT7C	0		Т	A11	PT8E	1		Т	A11	PT12A	1		Т
GND	GND	-			GND	GND	-			GND	GND	-		
B10	PT5D	0		С	B10	PT8D	1		С	B10	PT11B	1		С
B9	PT5C	0		Т	B9	PT8C	1		Т	B9	PT11A	1		Т
D10	PT8D	0		С	D10	PT8B	1		С	D10	PT10F	1		с
D9	PT8C	0		Т	D9	PT8A	1		Т	D9	PT10E	1		Т
-	-				VCCI01	VCCI01	1		ļ	VCCI01	VCCI01	1		
-	-				GND	GNDI01	1			GND	GNDIO1	1		
C10	PT6D	0		С	C10	PT7F	1		С	C10	PT10D	1		С
C9	PT6C	0		Т	C9	PT7E	1		Т	C9	PT10C	1		Т
A9	PT6B	0	PCLK0_1****	С	A9	PT7D	1	PCLK1_1****	С	A9	PT10B	1	PCLK1_1****	С
A10	PT6A	0		Т	A10	PT7C	1		Т	A10	PT10A	1		Т
E9	PT9B	0		С	E9	PT7B	1		С	E9	PT9D	1		с
E8	PT9A	0		Т	E8	PT7A	1		Т	E8	PT9C	1		Т
D7	PT5B	0	PCLK0_0****	С	D7	PT6F	0	PCLK1_0****	С	D7	PT9B	1	PCLK1_0****	С



		LAM)	(0640				LAN	IXO1200				LAN	/IXO2280	
Ball	Ball		Dual Function	Differential	Ball	Ball	Bank	Dual Function	Differential	Ball	Ball	Bank	Dual Function	Differential
Number	Function				Number	Function				Number	Function			
D8	PT5A	0		Т	D8	PT6E	0		Т	D8	PT9A	1		Т
VCCI00	VCCI00	0			VCCI00	VCCI00	0			VCCI00	VCCI00	0		
GND	GNDI00	0			GND	GNDI00	0			GND	GNDIO0	0		
C8	PT4F	0		С	C8	PT6D	0		С	C8	PT8D	0		С
B8	PT4E	0		Т	B8	PT6C	0		Т	B8	PT8C	0		Т
A8	VCCAUX	-			A8	VCCAUX	-			A8	VCCAUX	-		
A7	PT4D	0		С	A7	PT6B	0		С	A7	PT7D	0		С
A6	PT4C	0		Т	A6	PT6A	0		Т	A6	PT7C	0		Т
B7	PT4B	0		С	B7	PT5F	0		С	B7	PT7B	0		С
B6	PT4A	0		Т	B6	PT5E	0		Т	B6	PT7A	0		Т
C6	PT3C	0		Т	C6	PT5C	0		Т	C6	PT6A	0		Т
C7	PT3D	0		С	C7	PT5D	0		C	C7	PT6B	0		С
A5	PT3E	0		Т	A5	PT5A	0		Т	A5	PT6C	0		Т
A4	PT3F	0		С	A4	PT5B	0		С	A4	PT6D	0		С
E7	NC				E7	PT4C	0		Т	E7	PT6E	0		Т
E6	NC				E6	PT4D	0		С	E6	PT6F	0		С
B5	PT3B	0		С	B5	PT3F	0		C	B5	PT5D	0		C
B4	PT3A	0		Т	B4	PT3E	0		Т	B4	PT5C	0		Т
D5	PT2D	0		C	D5	PT3D	0		C	D5	PT5B	0		C
D6	PT2C	0		T	D6	PT3C	0		Т	D6	PT5A	0		T
C4	PT2E	0		Т	C4	PT4A	0		Т	C4	PT4A	0		Т
C5	PT2F	0		C	C5	PT4B	0		C	C5	PT4B	0		C
-	-	-			-	-	-			GND	GND	-		
D4	NC				D4	PT2D	0		С	D4	PT3D	0		С
D3	NC				D3	PT2C	0		т	D3	PT3C	0		T
A3	PT2B	0		С	A3	PT3B	0		C	A3	PT3B	0		C
A3 A2	PT2B PT2A	0		т	A3 A2	PT3B PT3A	0		т	A3 A2	PT3B PT3A	0		т
B3	NC	0		I	B3	PT3A PT2B	0		C	B3	PT3A PT2D	0		C
BS B2	NC				B2		0		Т	B2	PT2D PT2C	0		Т
		0				PT2A			1					1
VCCI00	VCCI00	0			VCCI00	VCCI00	0			VCCI00	VCCIO0	0		
GND	GNDIO0	0			GND	GNDIO0	0			GND	GNDIO0	0		
A1	GND	-			A1	GND	-			A1	GND	-		
A16	GND	-			A16	GND	-			A16	GND	-		
F11	GND	-			F11	GND	-			F11	GND	-		
G8	GND	-			G8	GND	-			G8	GND	-		
G9	GND	-			G9	GND	-			G9	GND	-		
H7	GND	-			H7	GND	-			H7	GND	-		
H8	GND	-			H8	GND	-			H8	GND	-		
H9	GND	-			H9	GND	-			H9	GND	-		
H10	GND	-			H10	GND	-			H10	GND	-		
J7	GND	-			J7	GND	-			J7	GND	-		
J8	GND	-			J8	GND	-			J8	GND	-		
19	GND	-			J9	GND	-			19	GND	-		
J10	GND	-			J10	GND	-			J10	GND	-		
K8	GND	-	ļ		K8	GND	-			K8	GND	-		
К9	GND	-			К9	GND	-			К9	GND	-		
L6	GND	-	ļ		L6	GND	-			L6	GND	-		
T1	GND	-			T1	GND	-			T1	GND	-		
T16	GND	-			T16	GND	-			T16	GND	-		
G7	VCC	-			G7	VCC	-			G7	VCC	-		
G10	VCC	-			G10	VCC	-			G10	VCC	-		
K7	VCC	-			K7	VCC	-			К7	VCC	-		
K10	VCC	-			K10	VCC	-			K10	VCC	-		
H6	VCCIO3	3			H6	VCCI07	7			H6	VCCI07	7		
G6	VCCIO3	3			G6	VCCI07	7			G6	VCCI07	7		
K6	VCCIO3	3			K6	VCCIO6	6			K6	VCCIO6	6		
J6	VCCIO3	3			J6	VCCIO6	6			J6	VCCIO6	6		
L8	VCCIO2	2			L8	VCCI05	5			L8	VCCIO5	5		
L7	VCCIO2	2			L7	VCCIO5	5			L7	VCCIO5	5		
10	VCCIO2	2			L9	VCCIO4	4			L9	VCCIO4	4		
L9							-							



		LAM)	KO640			LAN	1XO1200				LAN	1XO2280	
Ball Number	Ball Function	-	Dual Function	 -	Ball Function	Bank	Dual Function	Differential	Ball Number	Ball Function	Bank	Dual Function	Differential
K11	VCCI01	1		K11	VCCIO3	3			K11	VCCIO3	3		
J11	VCCI01	1		J11	VCCIO3	3			J11	VCCIO3	3		
H11	VCCI01	1		H11	VCCIO2	2			H11	VCCIO2	2		
G11	VCCI01	1		G11	VCCIO2	2			G11	VCCIO2	2		
F9	VCCI00	0		F9	VCCI01	1			F9	VCCI01	1		
F10	VCCI00	0		F10	VCCI01	1			F10	VCCI01	1		
F8	VCCI00	0		F8	VCCI00	0			F8	VCCI00	0		
F7	VCCI00	0		F7	VCCI00	0			F7	VCCI00	0		

Notes:

LCMXO640 only. 1.

2. Supports true LVDS outputs.

3. NC for "E" devices.

4. Primary clock inputs are single-ended.

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# 4.9. LA-MachXO2280 Logic Signal Connections: 324 ftBGA

		LAMXO2280		
Ball Number	Ball Function	Bank	Dual Function	Differential
GND	GNDIO7	7		
VCCI07	VCCI07	7		
D4	PL2A	7	LUM0_PLLT_FB_A	Т
F5	PL2B	7	LUM0_PLLC_FB_A	С
B3	PL3A	7		T*
C3	PL3B	7		C*
E4	PL3C	7	LUM0_PLLT_IN_A	Т
G6	PL3D	7	LUM0_PLLC_IN_A	С
A1	PL4A	7		T*
B1	PL4B	7		C*
F4	PL4C	7		Т
VCC	VCC	-		
E3	PL4D	7		С
D2	PL5A	7		Т*
D3	PL5B	7		C*
G5	PL5C	7		Т
F3	PL5D	7		С
C2	PL6A	7		Т*
VCCI07	VCCI07	7		
GND	GNDIO7	7		
C1	PL6B	7		C*
H5	PL6C	7		Т
G4	PL6D	7		С
E2	PL7A	7		Т*
D1	PL7B	7	GSRN	C*
J6	PL7C	7		Т
H4	PL7D	7		С
F2	PL8A	7		Т*
E1	PL8B	7		С*
GND	GND	-		
J3	PL8C	7		Т
J5	PL8D	7		С
G3	PL9A	7		Т*
H3	PL9B	7		С*
K3	PL9C	7		Т
K5	PL9D	7		С
F1	PL10A	7		Т*
VCCI07	VCCI07	7		
GND	GNDIO7	7		
G1	PL10B	7		C*
K4	PL10C	7		Т
K6	PL10D	7		С
G2	PL11A	6		Т*
H2	PL11B	6		С*
L3	PL11C	6		Т
L5	PL11D	6		С

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	[	LAMXO2280		
Ball Number	Ball Function	Bank	Dual Function	Differential
H1	PL12A	6		T*
VCCIO6	VCCIO6	6		
GND	GNDIO6	6		
J2	PL12B	6		C*
L4	PL12C	6		Т
L6	PL12D	6		С
К2	PL13A	6		T*
K1	PL13B	6		C*
J1	PL13C	6		Т
VCC	VCC	-		
L2	PL13D	6		С
M5	PL14D	6		С
M3	PL14C	6	TSALL	Т
L1	PL14B	6		C*
M2	PL14A	6		Т*
M1	PL15A	6		Т*
N1	PL15B	6		C*
M6	PL15C	6		Т
M4	PL15D	6		С
VCCIO6	VCCIO6	6		
GND	GNDIO6	6		
P1	PL16A	6		T*
P2	PL16B	6		C*
N3	PL16C	6		Т
N4	PL16D	6		С
GND	GND	-		
T1	PL17A	6	LLM0_PLLT_FB_A	T*
R1	PL17B	6	LLM0_PLLC_FB_A	C*
P3	PL17C	6		Т
N5	PL17D	6		C
R3	PL18A	6	LLMO PLLT IN A	T*
R2	PL18B	6	LLM0_PLLC_IN_A	C*
P4	PL19A	6		т
N6	PL19B	6		C
U1	PL20A	6		<u>т</u>
VCCIO6	VCCIO6	6		
GND	GNDIO6	6		
GND	GNDIO5	5		
VCCIO5	VCCIO5	5		
T2	PL20B	6		С
P6	TMS	5	TMS	C
V1	PB2A	5		Т
U2		5		C
T3	PB2B	5		<u>т</u>
	PB2C	5	тси	1
N7	TCK	5	ТСК	
R4 R5	PB2D PB3A	5		<u>с</u> т



		LAMXO2280		
Ball Number	Ball Function	Bank	Dual Function	Differential
T4	PB3B	5		С
VCC	VCC	-		
R6	PB3C	5		Т
P7	PB3D	5		С
U3	PB4A	5		T
T5	PB4B	5		С
V2	PB4C	5		Т
N8	TDO	5	TDO	
V3	PB4D	5		С
Т6	PB5A	5		Т
GND	GNDIO5	5		
VCCIO5	VCCIO5	5		
U4	PB5B	5		С
P8	PB5C	5		Т
T7	PB5D	5		С
V4	TDI	5	TDI	
R8	PB6A	5		Т
N9	PB6B	5		С
U5	PB6C	5		Т
V5	PB6D	5		С
U6	PB7A	5		Т
VCC	VCC	-		
V6	PB7B	5		С
P9	PB7C	5		T
T8	PB7D	5		С
U7	PB8A	5		T
V7	PB8B	5		С
M10	VCCAUX	-		
U8	PB8C	5		T
V8	PB8D	5		С
VCCIO5	VCCIO5	5		
GND	GNDIO5	5		
Т9	PB8E	5		Т
U9	PB8F	5		С
V9	PB9A	4		Т
V10	PB9B	4		С
N10	PB9C	4		Т
R10	PB9D	4		С
P10	PB10F	4	PCLK4_1**	С
T10	PB10E	4		T
U10	PB10D	4		С
V11	PB10C	4		T
U11	PB10B	4	PCLK4_0**	C
VCCIO4	VCCIO4	4		-
GND	GNDIO4	4		
T11	PB10A	4		Т
U12	PB11A	4		<u>т</u>



		LAMXO2280		
Ball Number	Ball Function	Bank	Dual Function	Differential
R11	PB11B	4		C
GND	GND	-		
T12	PB11C	4		Т
P11	PB11D	4		С
V12	PB12A	4		Т
V13	PB12B	4		С
R12	PB12C	4		Т
N11	PB12D	4		С
U13	PB12E	4		Т
VCCIO4	VCCIO4	4		
GND	GNDIO4	4		
V14	PB12F	4		С
T13	PB13A	4		Т
P12	PB13B	4		С
R13	PB13C	4		Т
N12	PB13D	4		С
V15	PB14A	4		Т
U14	PB14B	4		С
V16	PB14C	4		Т
GND	GND	-		
T14	PB14D	4		С
U15	PB15A	4		Т
V17	PB15B	4		С
P13	NC	-		
T15	PB15D	4		
U16	PB16A	4		Т
V18	PB16B	4		С
N13	PB16C	4		Т
R14	PB16D	4		С
VCCIO4	VCCIO4	4		
GND	GNDIO4	4		
GND	GNDIO3	3		
VCCIO3	VCCIO3	3		
P15	PR20B	3		С
N14	PR20A	3		Т
N15	PR19B	3		С
M13	PR19A	3		Т
R15	PR18B	3		C*
T16	PR18A	3		Т*
N16	PR17D	3		С
M14	PR17C	3		Т
U17	PR17B	3		C*
VCC	VCC	-		-
U18	PR17A	3		Т*
R17	PR16D	3		C
R16	PR16C	3		т
P16	PR16B	3		C*



	LAMXO2280			
Ball Number	Ball Function	Bank	Dual Function	Differential
VCCIO3	VCCIO3	3		
GND	GNDIO3	3		
P17	PR16A	3		Т*
L13	PR15D	3		С
M15	PR15C	3		Т
T17	PR15B	3		C*
T18	PR15A	3		Т*
L14	PR14D	3		С
L15	PR14C	3		Т
R18	PR14B	3		C*
P18	PR14A	3		Т*
GND	GND	-		
K15	PR13D	3		С
K13	PR13C	3		Т
N17	PR13B	3		C*
N18	PR13A	3		Т*
K16	PR12D	3		С
K14	PR12C	3		Т
M16	PR12B	3		C*
L16	PR12A	3		Т*
GND	GNDIO3	3		
VCCIO3	VCCIO3	3		
J16	PR11D	3		С
J14	PR11C	3		Т
M17	PR11B	3		C*
L17	PR11A	3		Т*
J15	PR10D	2		С
J13	PR10C	2		Т
M18	PR10B	2		C*
L18	PR10A	2		T*
GND	GNDIO2	2		
VCCIO2	VCCIO2	2		
H16	PR9D	2		С
H14	PR9C	2		T
K18	PR9B	2		C*
J18	PR9A	2		T*
J17	PR8D	2		C
VCC	VCC			
H18	PR8C	2		Т
H17	PR8B	2		C*
G17	PR8A	2		T*
H13	PR7D	2		C
H15	PR7C	2		т
G18	PR7B	2		C*
F18	PR7A	2		
G14	PR6D	2		C
G16	PR6C	2		т



LAMXO2280				
Ball Number	Ball Function	Bank	Dual Function	Differential
VCCIO2	VCCIO2	2		
GND	GNDIO2	2		
E18	PR6B	2		C*
F17	PR6A	2		Т*
G13	PR5D	2		С
G15	PR5C	2		Т
E17	PR5B	2		C*
E16	PR5A	2		Т*
GND	GND	-		
F15	PR4D	2		С
E15	PR4C	2		Т
D17	PR4B	2		C*
D18	PR4A	2		Т*
B18	PR3D	2		С
C18	PR3C	2		Т
C16	PR3B	2		C*
D16	PR3A	2		T*
C17	PR2B	2		С
D15	PR2A	2		Т
VCCIO2	VCCIO2	2		
GND	GNDIO2	2		
GND	GNDIO1	1		
VCCI01	VCCI01	1		
E13	PT16D	1		С
C15	PT16C	1		Т
F13	PT16B	1		С
D14	PT16A	1		Т
A18	PT15D	1		С
B17	PT15C	1		Т
A16	PT15B	1		С
A17	PT15A	1		Т
VCC	VCC	-		
D13	PT14D	1		С
F12	PT14C	1		Т
C14	PT14B	1		С
E12	PT14A	1		Т
C13	PT13D	1		С
B16	PT13C	1		Т
B15	PT13B	1		С
A15	PT13A	1		Т
VCCI01	VCCI01	1		
GND	GNDIO1	1		
B14	PT12F	1		С
A14	PT12E	1		 T
D12	PT12D	1		C
F11	PT12C	1		T
B13	PT128	1		C



	LAMXO2280			
Ball Number	Ball Function	Bank	Dual Function	Differential
A13	PT12A	1		Т
C12	PT11D	1		С
GND	GND	-		
B12	PT11C	1		Т
E11	PT11B	1		С
D11	PT11A	1		Т
C11	PT10F	1		С
A12	PT10E	1		Т
VCCI01	VCCI01	1		
GND	GNDIO1	1		
F10	PT10D	1		С
D10	PT10C	1		Т
B11	PT10B	1	PCLK1_1***	С
A11	PT10A	1		Т
E10	PT9D	1		С
C10	PT9C	1		Т
D9	РТ9В	1	PCLK1_0***	С
E9	PT9A	1		Т
B10	PT8F	0		С
A10	PT8E	0		Т
VCCI00	VCCI00	0		
GND	GNDIO0	0		
A9	PT8D	0		С
С9	PT8C	0		Т
В9	PT8B	0		С
F9	VCCAUX	-		
A8	PT8A	0		Т
B8	PT7D	0		С
C8	PT7C	0		Т
VCC	VCC	-		
A7	PT7B	0		С
B7	PT7A	0		Т
A6	PT6A	0		Т
B6	PT6B	0		С
D8	PT6C	0		Т
F8	PT6D	0		С
C7	PT6E	0		Т
E8	PT6F	0		С
D7	PT5D	0		С
VCCI00	VCCIO0	0		
GND	GNDIO0	0		
E7	PT5C	0		Т
A5	PT5B	0		С
C6	PT5A	0		Т
B5	PT4A	0		Т
A4	PT4B	0		С
D6	PT4C	0		Т



LAMXO2280				
Ball Number	Ball Function	Bank	Dual Function	Differential
F7	PT4D	0		С
B4	PT4E	0		Т
GND	GND	-		
C5	PT4F	0		C
F6	PT3D	0		С
E5	PT3C	0		Т
E6	PT3B	0		С
D5	PT3A	0		Т
A3	PT2D	0		C
C4	PT2C	0		Т
A2	PT2B	0		С
B2	PT2A	0		Т
VCCI00	VCCI00	0		
GND	GNDIO0	0		
E14	GND	-		
F16	GND	-		
H10	GND	-		
H11	GND	-		
H8	GND	-		
H9	GND	-		
J10	GND	-		
J11	GND	-		
J4	GND	-		
J8	GND	-		
J9	GND	-		
K10	GND	_		
K11	GND	_		
K17	GND	_		
K8	GND	_		
К9	GND	_		
L10	GND	-		
L11	GND	-		
 L8	GND	_		
L9	GND	_		
N2	GND	-		
P14	GND	-		
P5	GND	-		
 R7	GND	-		
F14	VCC	-		
G11	VCC			
G11 G9	VCC	-		
		-		
H7	VCC	-		
L7	VCC	-		
M9	VCC	- 7		
H6	VCCIO7	7		
J7 M7	VCCIO7 VCCIO6	7 6		



	LAMXO2280			
Ball Number	Ball Function	Bank	Dual Function	Differential
K7	VCCIO6	6		
M8	VCCIO5	5		
R9	VCCIO5	5		
M12	VCCIO4	4		
M11	VCCIO4	4		
L12	VCCIO3	3		
K12	VCCIO3	3		
J12	VCCIO2	2		
H12	VCCIO2	2		
G12	VCCI01	1		
G10	VCCI01	1		
G8	VCCI00	0		
G7	VCCI00	0		

#### Notes:

1. Supports true LVDS outputs.

2. Primary clock inputs are single-ended.

### 4.10. Thermal Management

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Designers must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Thermal Management document to find the device/package specific thermal values.

### 4.10.1. For Further Information

For further information regarding Thermal Management, refer to the following located on the Lattice website at www.latticesemi.com.

- Thermal Management document
- Technical Note TN1090 Power Estimation and Management for MachXO Devices
- Power Calculator tool included with Lattice's ispLEVER design tool, or as a standalone download from www.latticesemi.com/software

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# 5. Ordering Information

### 5.1. Part Number Description

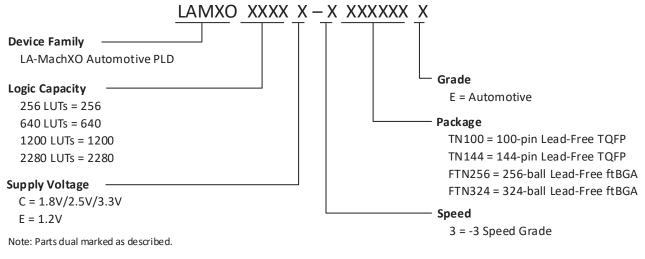


Figure 5.1.

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Part Number	LUTs	Supply Voltage	I/Os	Grade	Package	Pins	Temp.
LAMXO256C-3TN100E	256	1.8 V/2.5 V/3.3 V	78	-3	Lead-Free TQFP	100	AUTO
LAMXO640C-3TN100E	640	1.8 V/2.5 V/3.3 V	74	-3	Lead-Free TQFP	100	AUTO
LAMXO640C-3TN144E	640	1.8 V/2.5 V/3.3 V	113	-3	Lead-Free TQFP	144	AUTO
LAMXO640C-3FTN256E	640	1.8 V/2.5 V/3.3 V	159	-3	Lead-Free ftBGA	256	AUTO
LAMXO256E-3TN100E	256	1.2 V	78	-3	Lead-Free TQFP	100	AUTO
LAMXO640E-3TN100E	640	1.2 V	74	-3	Lead-Free TQFP	100	AUTO
LAMXO640E-3TN144E	640	1.2 V	113	-3	Lead-Free TQFP	144	AUTO
LAMXO640E-3FTN256E	640	1.2 V	159	-3	Lead-Free ftBGA	256	AUTO
LAMXO1200E-3TN100E	1200	1.2 V	73	-3	Lead-Free TQFP	100	AUTO
LAMXO1200E-3TN144E	1200	1.2 V	113	-3	Lead-Free TQFP	144	AUTO
LAMXO1200E-3FTN256E	1200	1.2 V	211	-3	Lead-Free ftBGA	256	AUTO
LAMXO2280E-3TN100E	2280	1.2 V	73	-3	Lead-Free TQFP	100	AUTO
LAMXO2280E-3TN144E	2280	1.2 V	113	-3	Lead-Free TQFP	144	AUTO
LAMXO2280E-3FTN256E	2280	1.2 V	211	-3	Lead-Free ftBGA	256	AUTO
LAMXO2280E-3FTN324E	2280	1.2 V	271	-3	Lead-Free ftBGA	324	AUTO

### 5.2. Ordering Information

# 6. Supplemental Information

### 6.1. For Further Information

A variety of technical notes for the LA-MachXO family are available on the Lattice web site at www.latticesemi.com.

- MachXO sysIO Usage Guide (FPGA-TN-02169)
- MachXO sysCLOCK PLL Design and Usage Guide (FPGA-TN-02168)
- MachXO Memory Usage Guide (FPGA-TN-02170)
- Power Estimation and Management for MachXO Devices (FPGA-TN-02171)
- MachXO JTAG Programming and Configuration User's Guide (FPGA-TN-02167)
- Minimizing System Interruption During Configuration Using TransFR Technology (FPGA-TN-02025-37)
- MachXO Density Migration (FPGA-TN-02165)
- IEEE 1149.1 Boundary Scan Testability in Lattice Devices

For further information on interface standards refer to the following web sites:

- JEDEC Standards (LVTTL, LVCMOS): www.jedec.org
- PCI: www.pcisig.com

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# **Technical Support Assistance**

Submit a technical support case through www.latticesemi.com/techsupport.

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# **Revision History**

#### Revision 1.6, December 2019

Section	Change Summary	
All	Changed document number from DS1003 to FPGA-DS-02070.	
	Updated document template.	
Disclaimers	Added this section.	

#### Revision 1.5, November 2007

Section	Change Summary	
DC and Switching Characteristics	Updated sysIO Single-Ended DC Electrical Characteristics table.	
	Added JTAG Port Timing Waveforms diagram.	
Pinout Information	Added Thermal Management text section.	
Supplemental Information	Updated title list.	

#### Revision 1.4, February 2007

Section	Change Summary
Architecture	Updated EBR Asynchronous Reset section.

#### Revision 1.3, December 2006

Section	Change Summary	
Architecture	EBR Asynchronous Reset section added.	
Pinout Information	Power Supply and NC table: Pin/Ball orientation footnotes added.	

#### Revision 1.2, November 2006

Section	Change Summary	
DC and Switching Characteristics	<ul> <li>Corrections to MachXO "C" Sleep Mode Timing table - value for t<sub>WSLEEPN</sub> (400 ns) changed from max. to min. Value for t<sub>WAWAKE</sub> (100 ns) changed from min. to max.</li> <li>Added Flash Download Time table.</li> </ul>	

#### Revision 1.1, May 2006

Section	Cha	Change Summary	
Pinout Information	٠	Removed [LOC][0]_PLL_RST from Signal Descriptions table.	
	٠	PCLK footnote added to appropriate pins in Logic Signal Connections tables.	

#### Revision 1.0, April 2006

Section	Change Summary
All	Initial release.



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